



Optical metrology for energy production

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Material modelling scientist

Outline

Motivation

Scope, financial aspects

Who are we?

History, markets, approach

Light \leftrightarrow Electricity

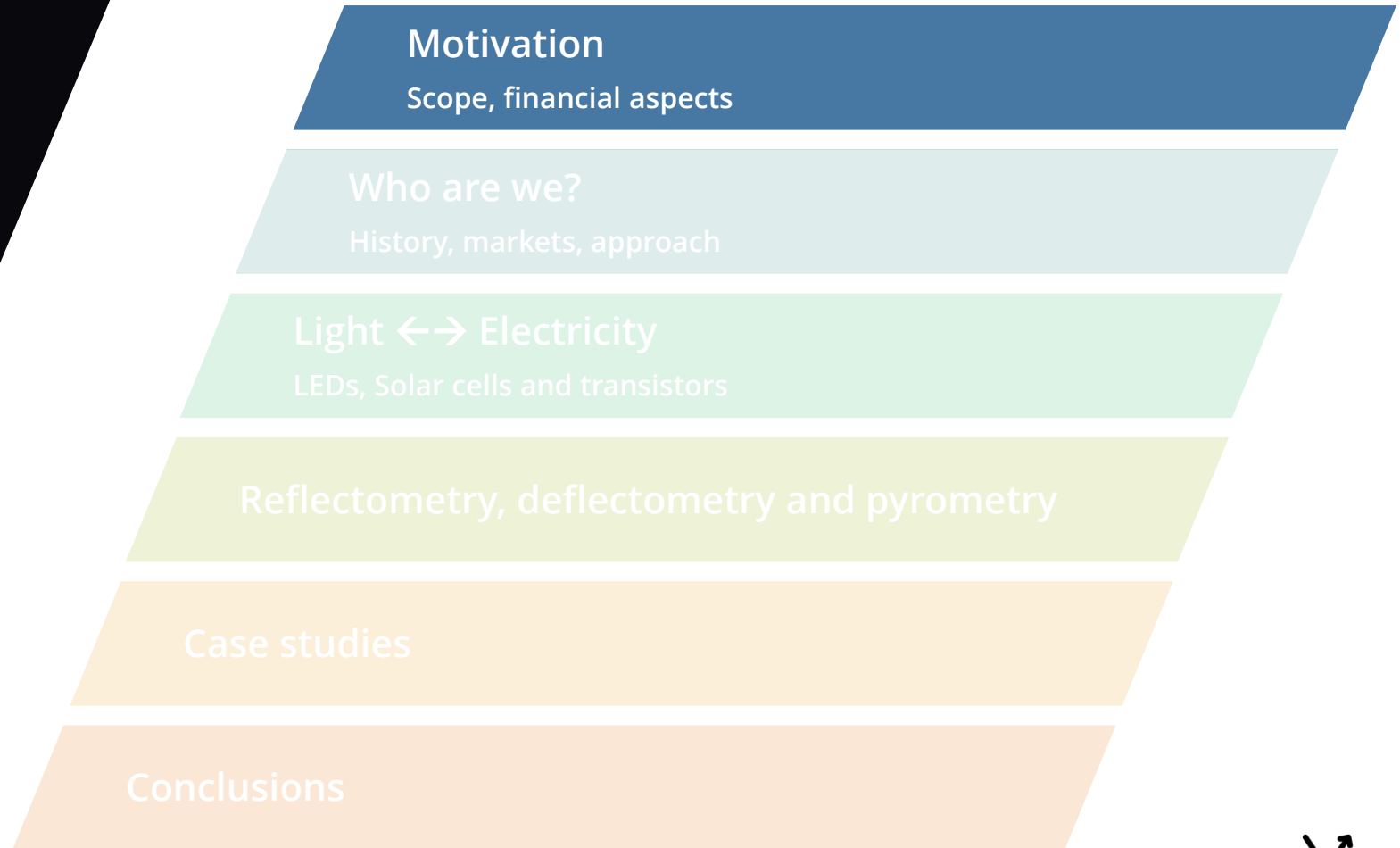
LEDs, Solar cells and transistors

Reflectometry, deflectometry and pyrometry

Case studies

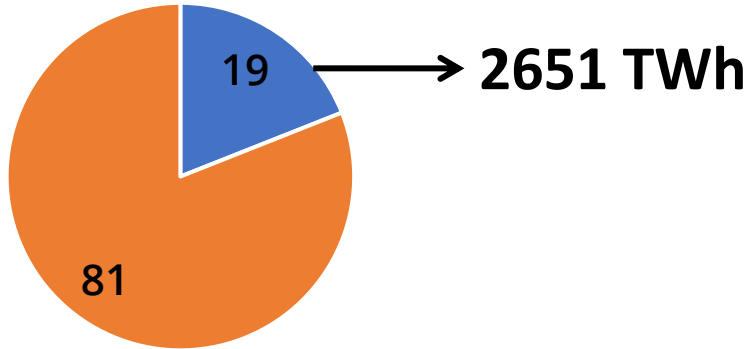
Conclusions

Outline



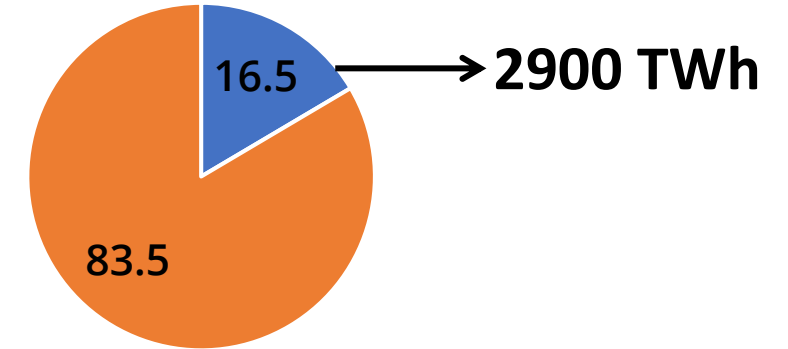
Interesting fact,1: solid-state lighting

Electricity production 2010



■ Lighting ■ Rest

Electricity production 2021



■ Lighting ■ Rest

Solid-state lighting
SSL

Thanks to the increase in efficiency and yield of SSL: For 800 lm

Incandescent lamp: 60 W

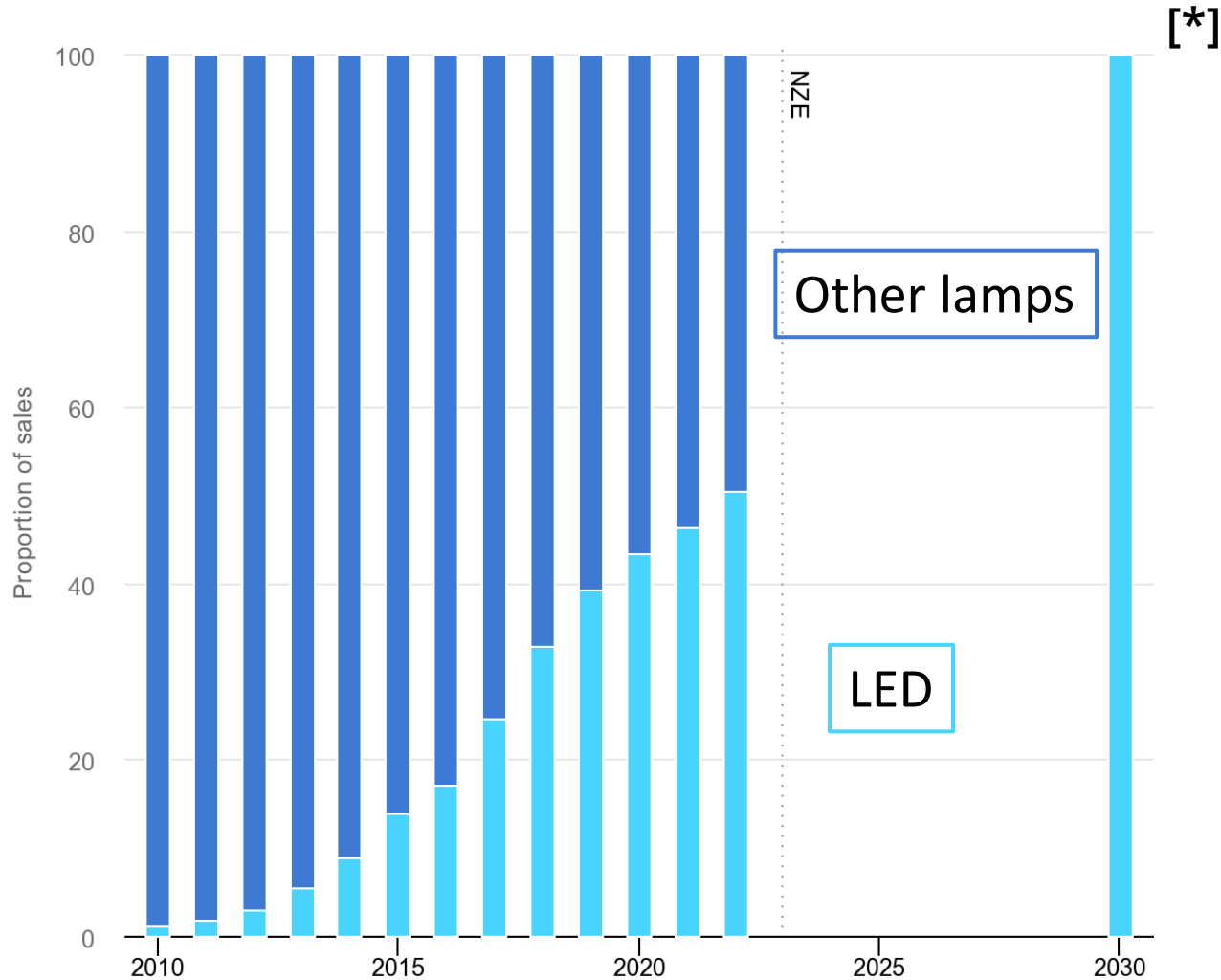
LED: 7-10 W

**The rebound effect?
Not there yet 😊**

* G. Zissis et al., Update on the Status of LED-Lighting world market since 2018, EUR 30500 EN, Publications Office of the European Union, Luxembourg, 2021

** <https://www.takethreelighting.com/lumen-watt-comparison.html>

Interesting fact,1

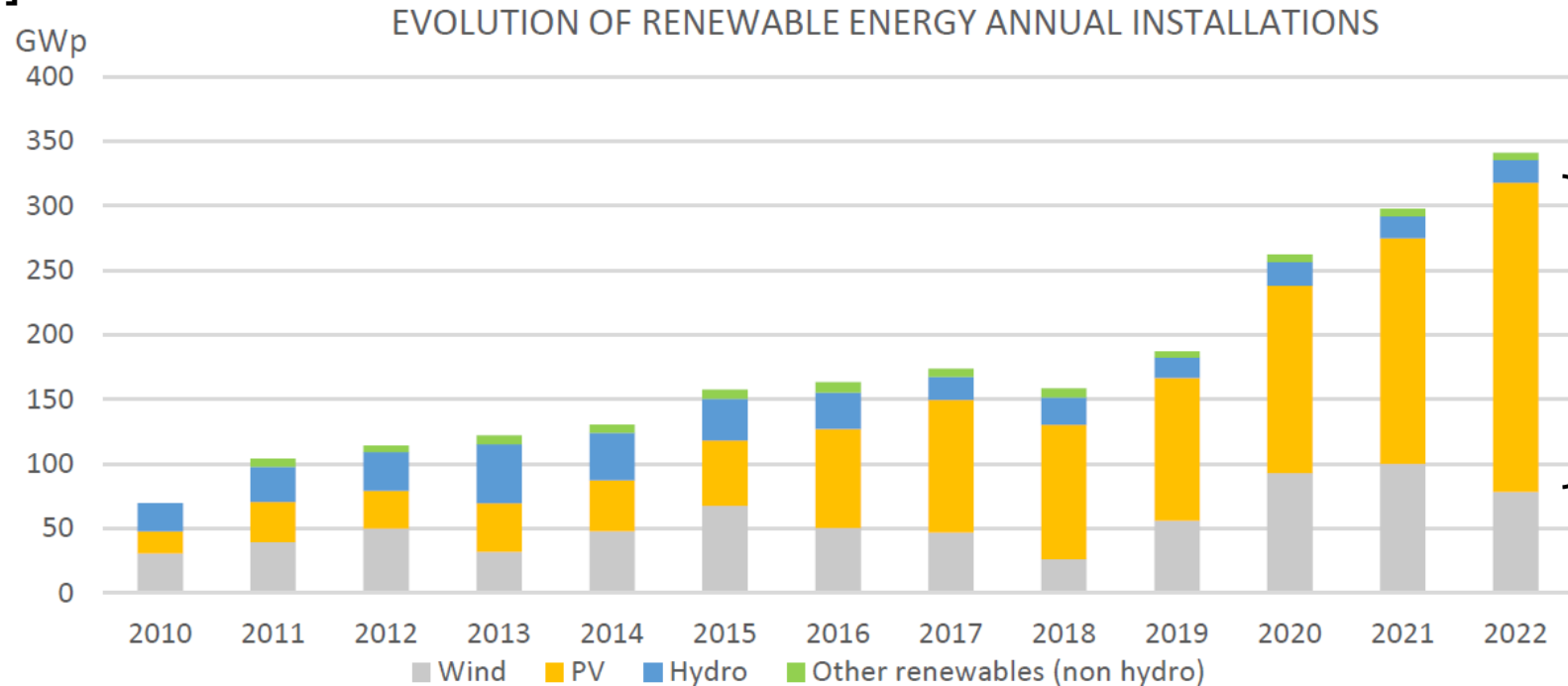


- Lighting is not neutral in terms of human health → **Wavelength matters!**
- Filtering harmful wavelengths
- Specific applications, e.g. UV for medical use
- Uniformity

* IEA, *Global residential lighting sales share by technology in the Net Zero Scenario, 2010-2030*, IEA, Paris

Interesting fact,2: Photovoltaic technology

[*]

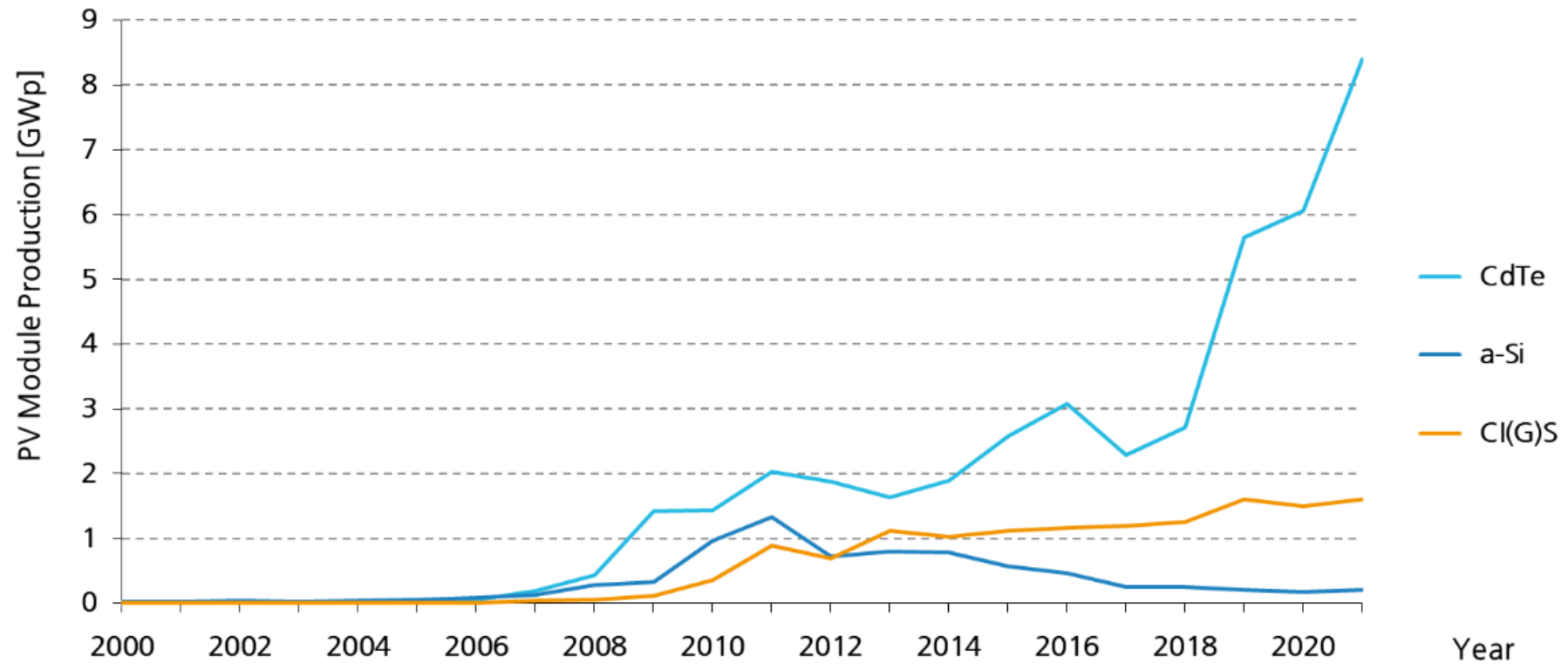


PV plays a major role in energy transition

- Consistent costs, technical performance and accessibility
- Faster permitting procedures

Interesting fact,2: Thin-film PV

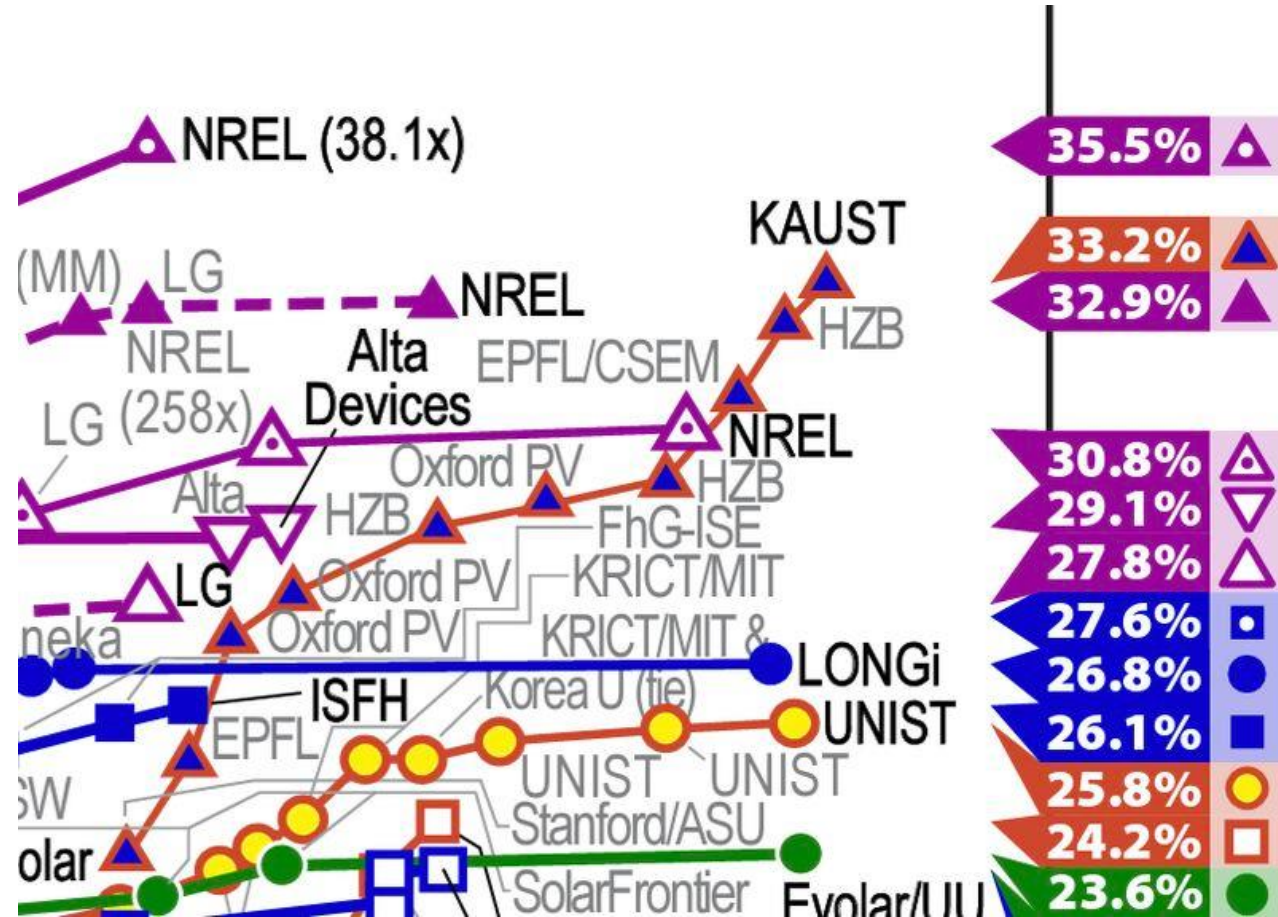
➤ ~%5 of the PV market is covered by thin-film solar cells *



* Fraunhofer ISE: Photovoltaics Report, updated: 21 February 2023

Interesting fact,2: Future of thin-film PV

➤ Perovskites are expected to change the equation soon!



Si/Perovskite tandem

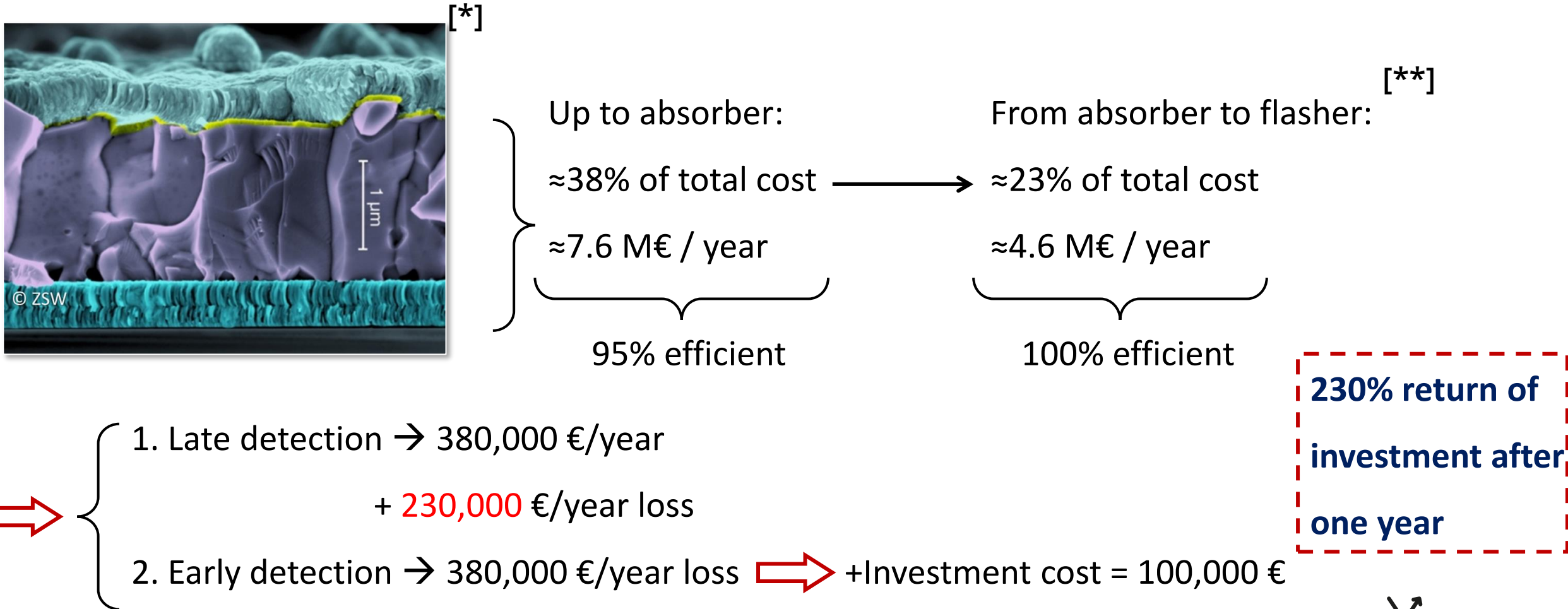
Si only

- Only affordable PV technology proven to surpass Si efficiency
- Si hitting physical limits
- Tandem production lines can be added to the existing Si lines



* Image credits: <https://www.nrel.gov/pv/cell-efficiency.html>

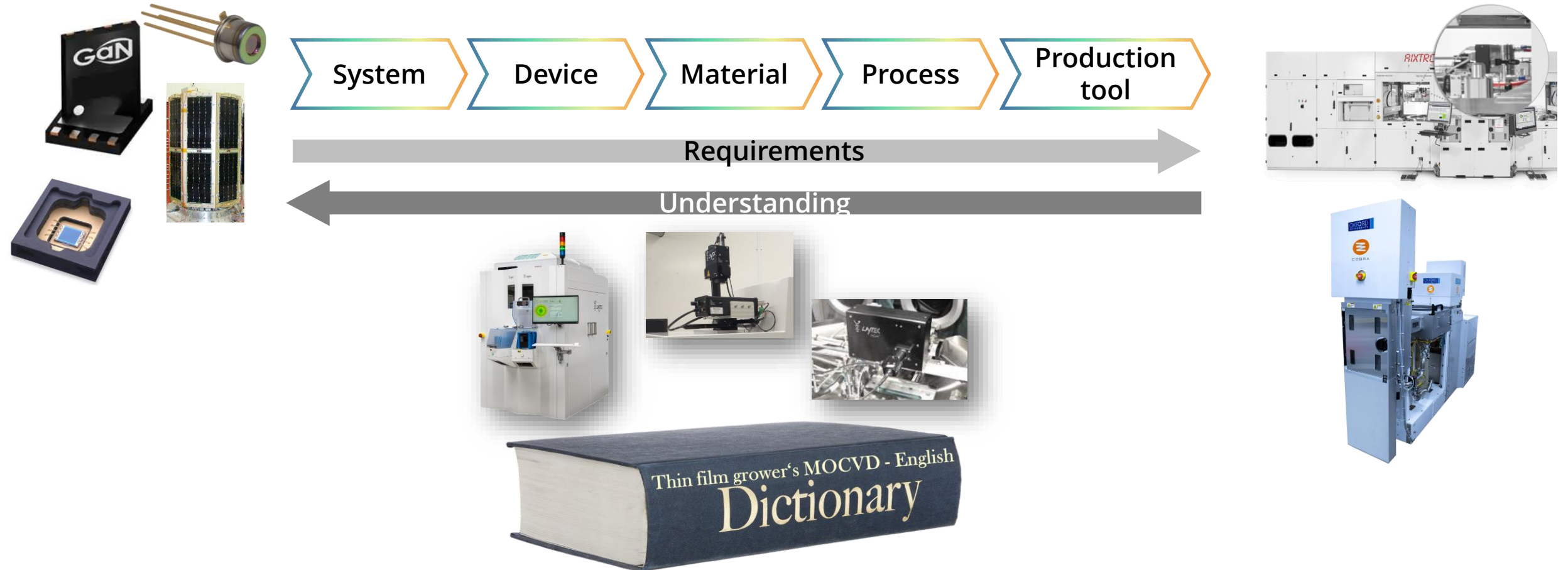
Economic value of metrology: Example thin film solar cells (simplified)



* Zentrum für Sonnenenergie- und Wasserstoff-Forschung (ZSW), www.zsw-bw.de

** K. A. W. Horowitz et al., NREL/PR-6A20-64507, 2015

On the road to higher performance, higher yield and lower cost ...



→ Metrology helps you to understand – metrology can be your dictionary!

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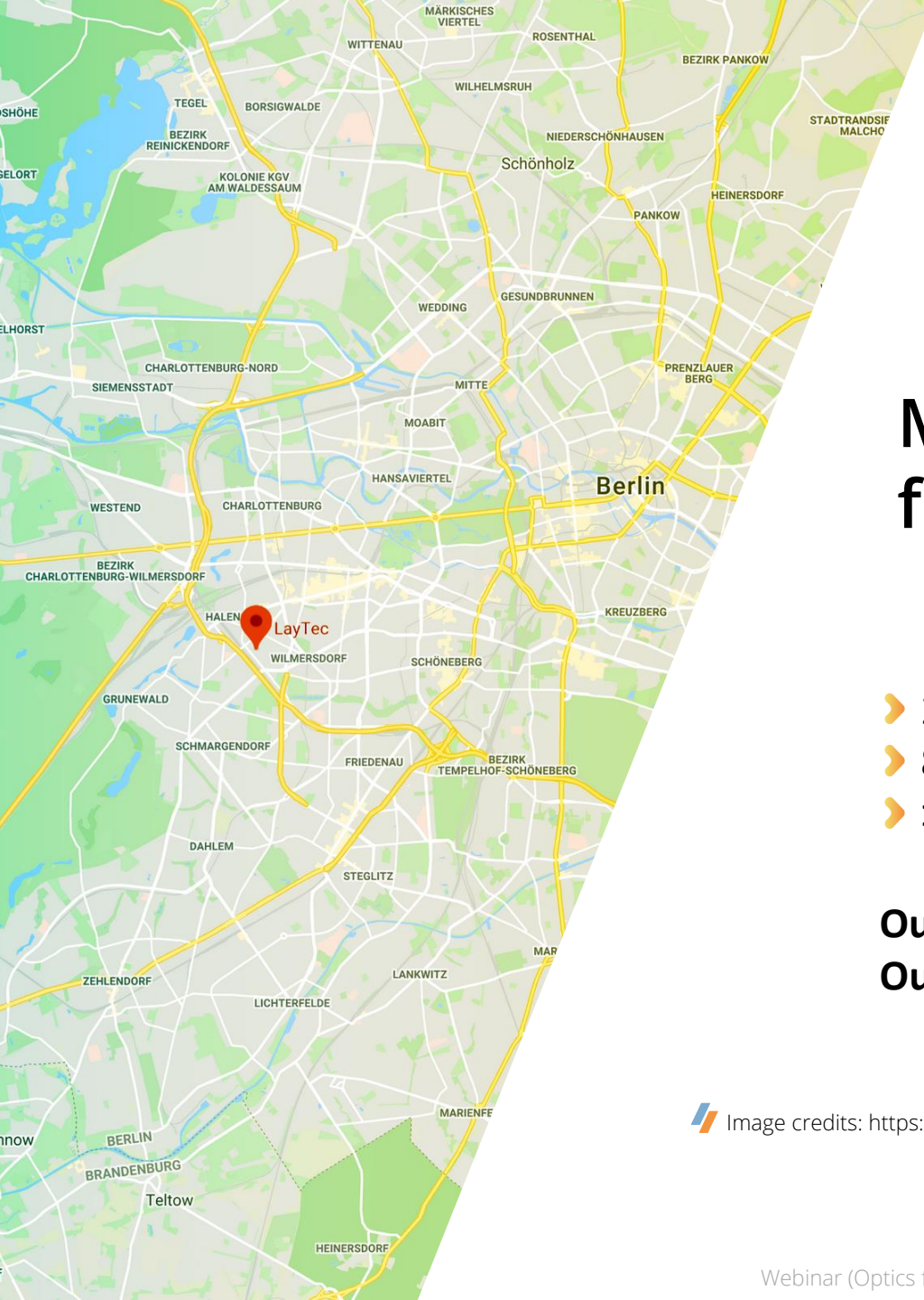
Light \leftrightarrow Electricity

LEDs, Solar cells and transistors

Reflectometry, deflectometry and pyrometry

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Metrology company founded 1999 in Berlin

- 24 years old
- 85 employees
- >3500 systems sold
- Spin-off of TU Berlin
- Operating worldwide
- Member of Nynomic group

Our business: Process-integrated optical metrology

Our markets: Semiconductor and thin-film industry & academia
incl. lighting, laser, PV, glass coating ...

 Image credits: <https://www.google.de/maps>

Integrated metrology for various industries and markets



Image credits: see last slide

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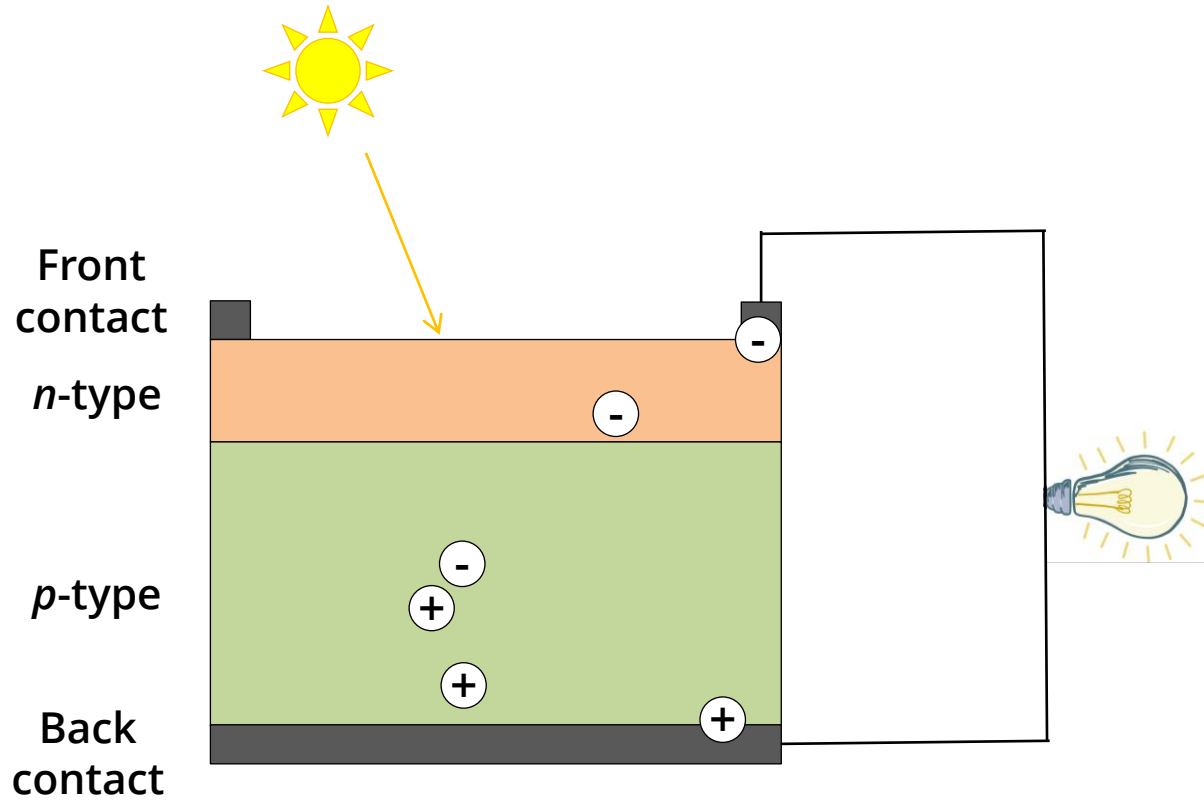
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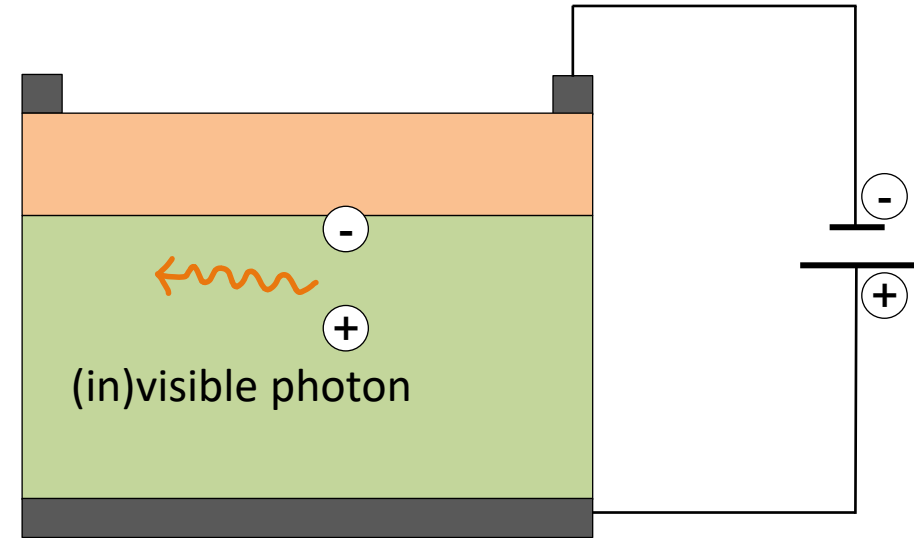
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Light ⇔ Electricity in simple words



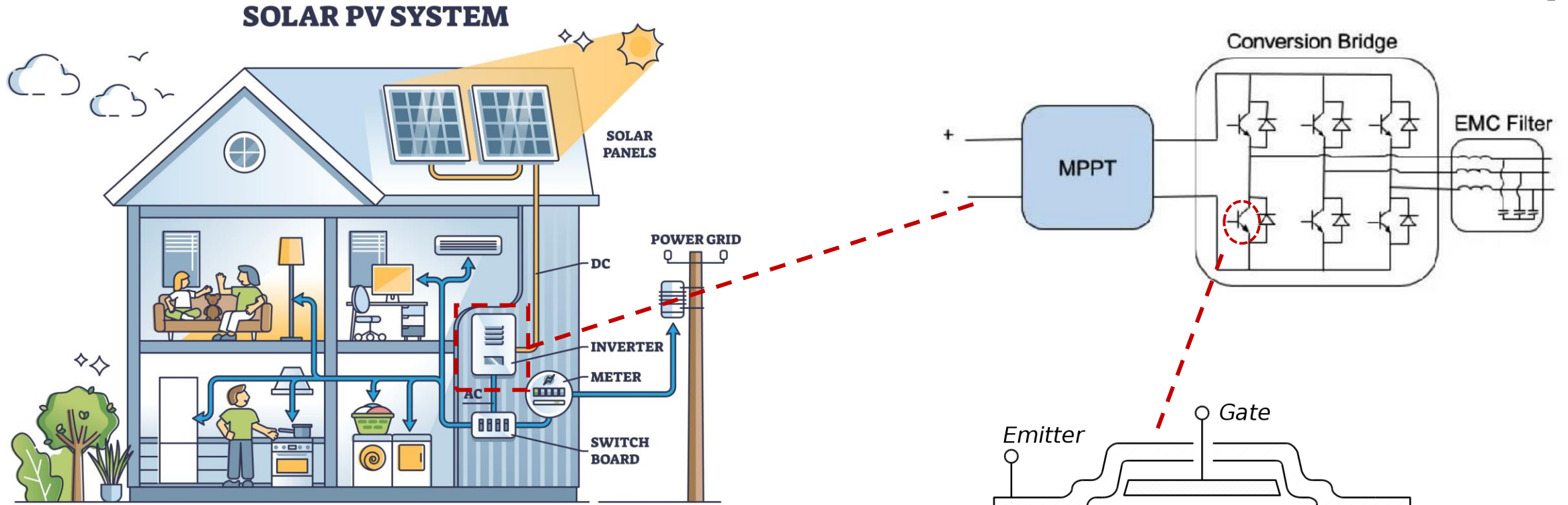
Solar cells



LEDs

Light ⇔ Electricity in simple words

[*]



Insulated gate bipolar transistors (IGBT)

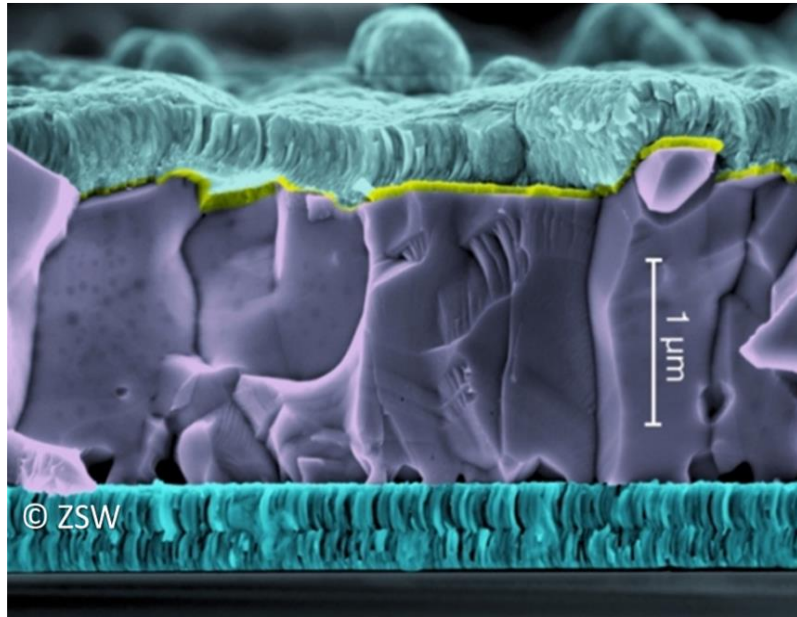
[**]



* <https://eepower.com/technical-articles/an-introduction-to-inverters-for-photovoltaic-pv-applications/#>

** Wikipedia: https://en.wikipedia.org/wiki/Insulated_gate_bipolar_transistor

CIGS solar cell [*]

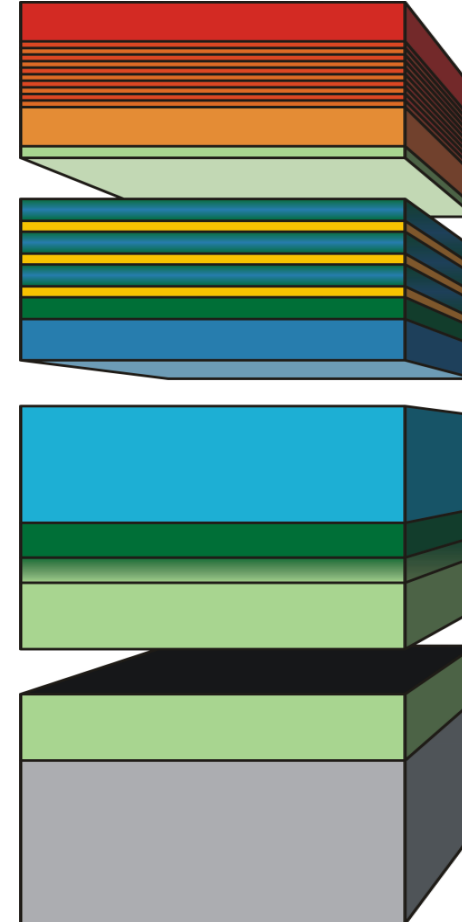


← ~50+ 200 nm
 ← ~50 nm
 ← < 2.5 μm
 ← ~500 μm

(In)AlGaIn MQWs
 $Al_xGa_{1-x}N$ transition

Deep UV LED[**]

p-GaN cap
 p-AlGaIn SPSL
 p-AlGaIn EBL



- Composition
- Temperature
- Curvature and strain
- Surface roughness

* Zentrum für Sonnenenergie- und Wasserstoff-Forschung (ZSW), www.zsw-bw.de
 ** Kneissl, M et al.. Nat. Photonics 13, 233–244 (2019). <https://doi.org/10.1038/s41566-019-0359-9>

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Interference is:

- Constructive at $2nd_1 = m\lambda$
- Destructive at $2nd_1 = (m+1/2)\lambda$

$r = \frac{r_{01} + r_{12}e^{-2i\beta}}{1 - r_{10}r_{12}e^{-2i\beta}}$ where $\beta = 2\pi \frac{d_1}{\lambda} \widehat{n}_1 \cos\varphi_1$

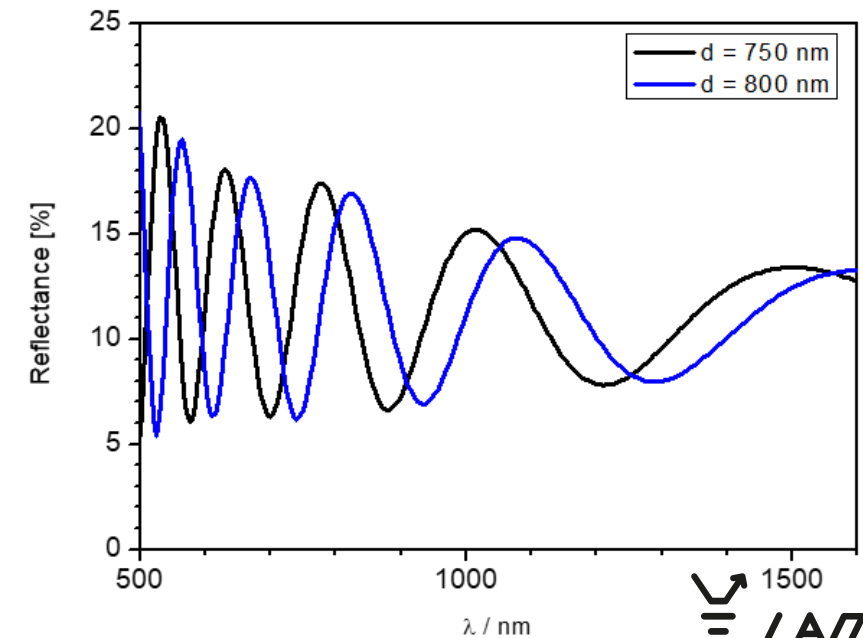
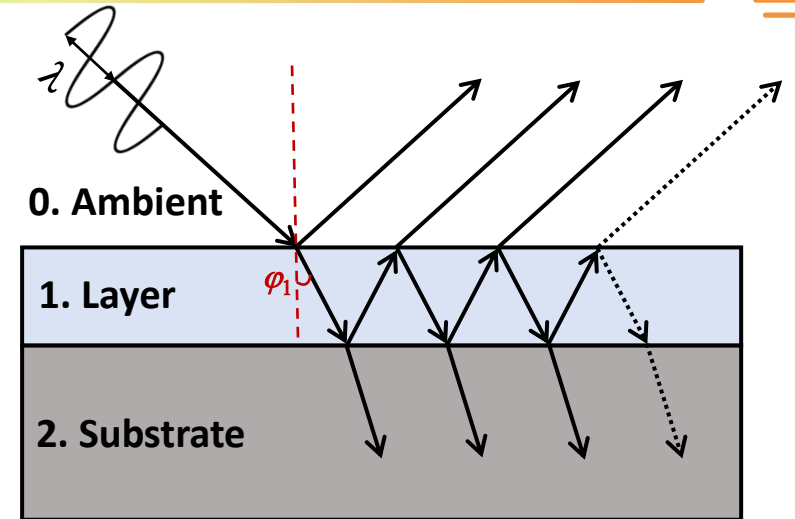
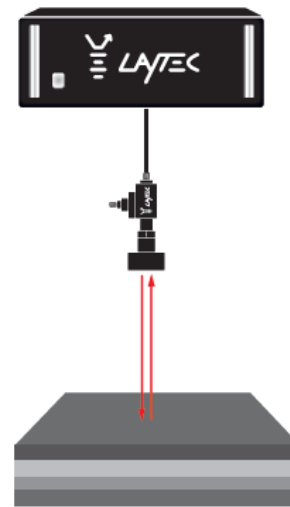
Reflectance, $R = |r|^2$

Light source

- White light
- Monochromatic

Fabry-Perot oscillations

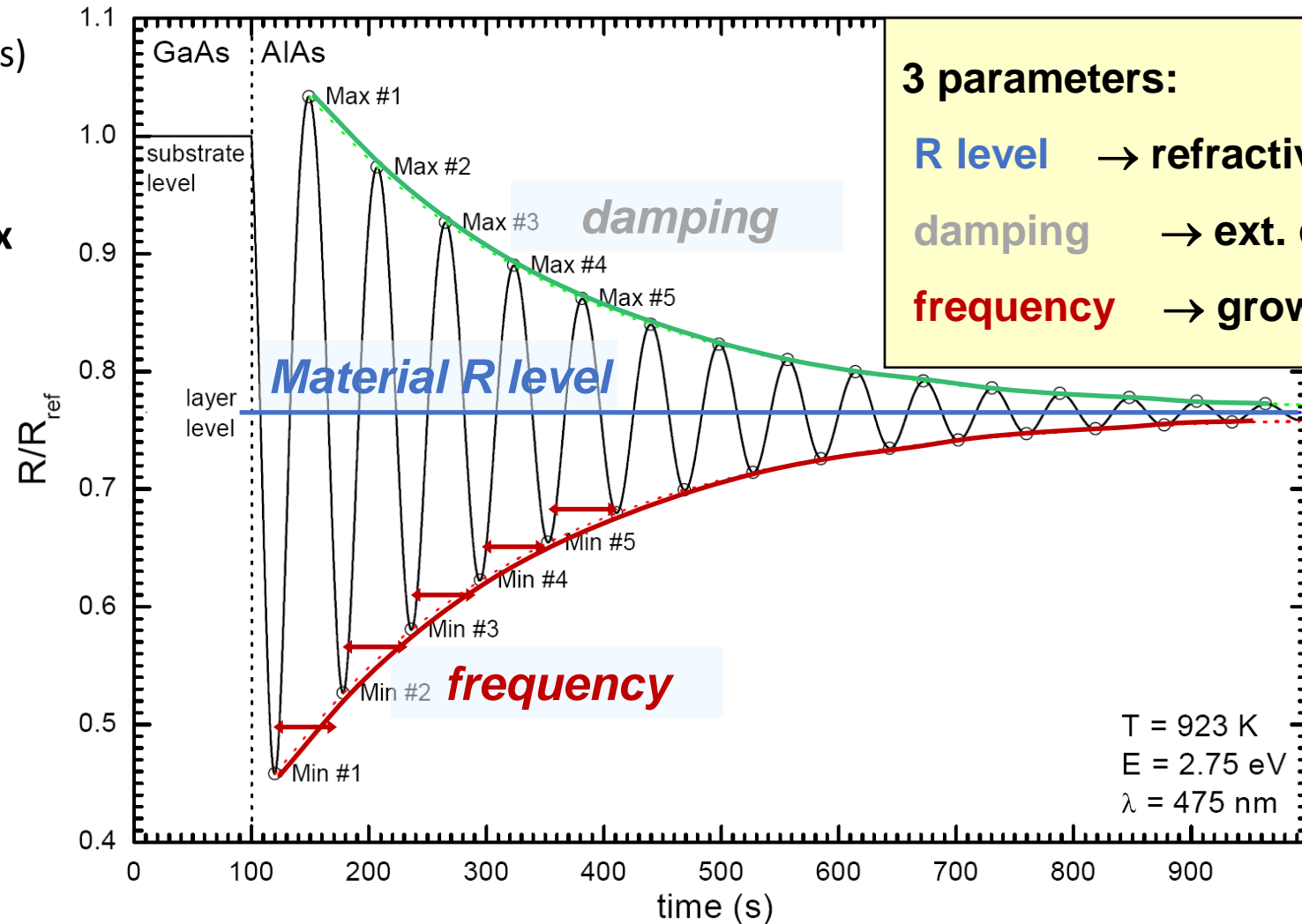
- Spectral
- Temporal (growth oscillations)



➤ Fabry-Perot oscillations

➤ Temporal (growth oscillations)

➔ Information on film thickness
(growth rate) and refractive index



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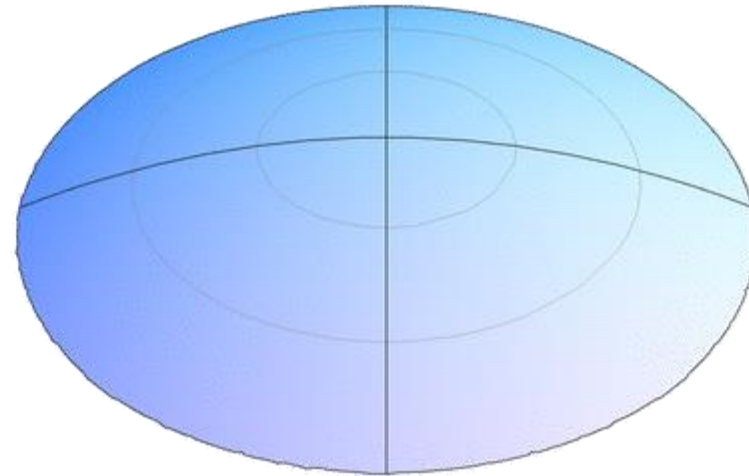
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**concave
upwards
positive curvature**

**convex
downwards
negative curvature**



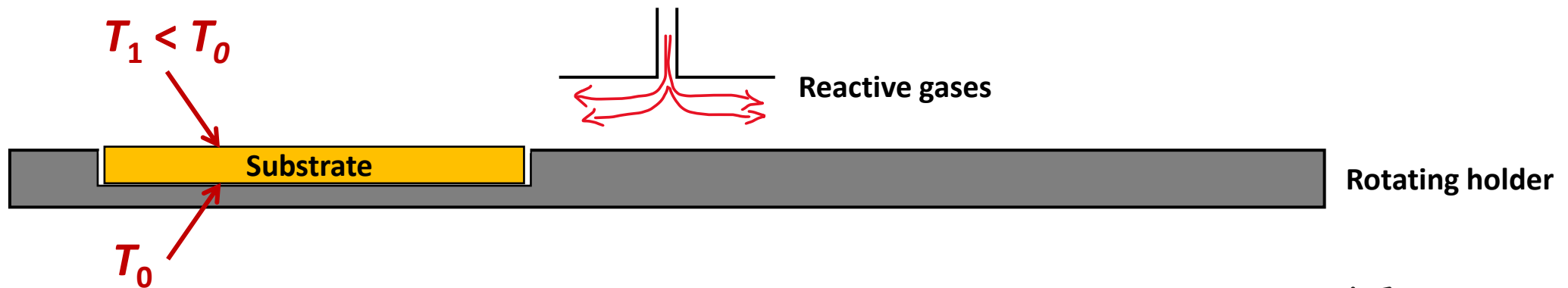
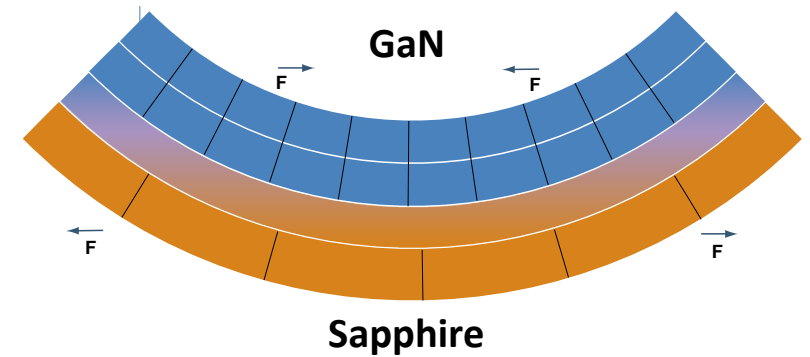
Concave

Flat

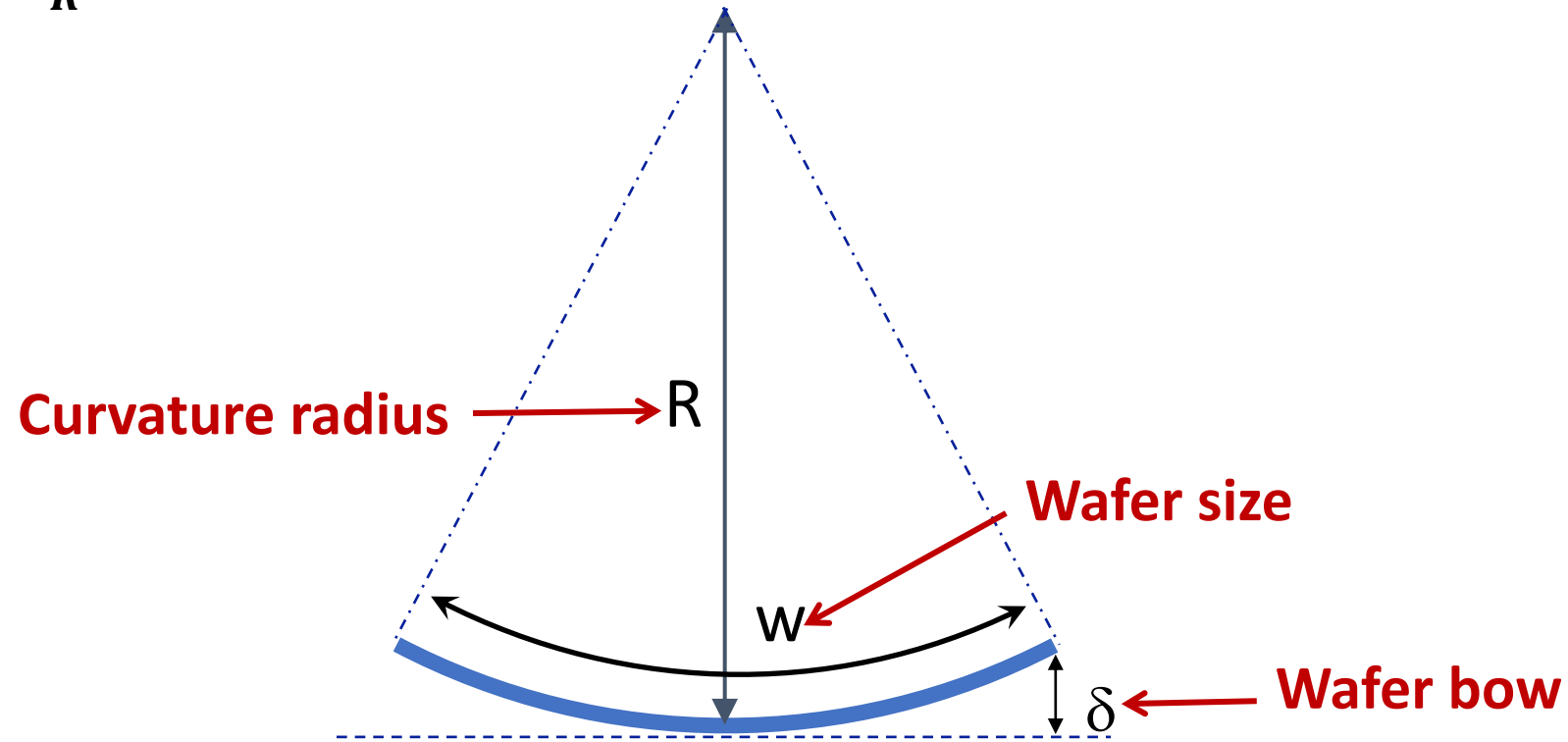
Convex

Why does it happen?

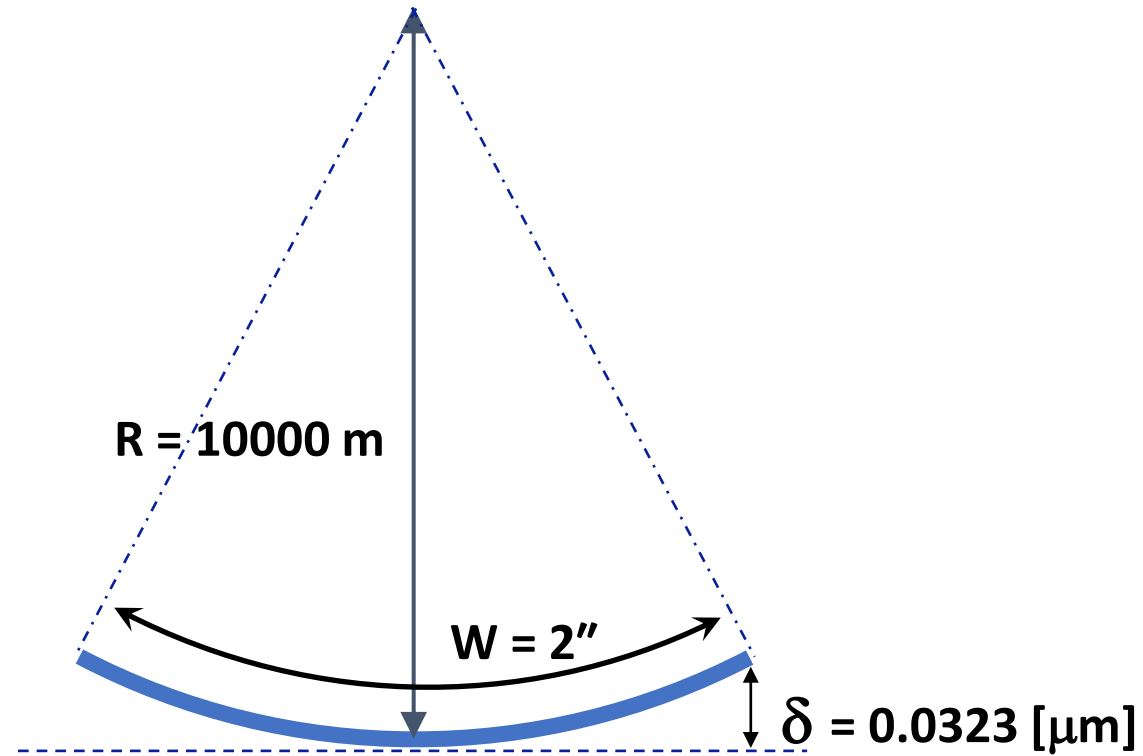
- Uneven temperature
- Lattice mismatch
- Thermal expansion mismatch



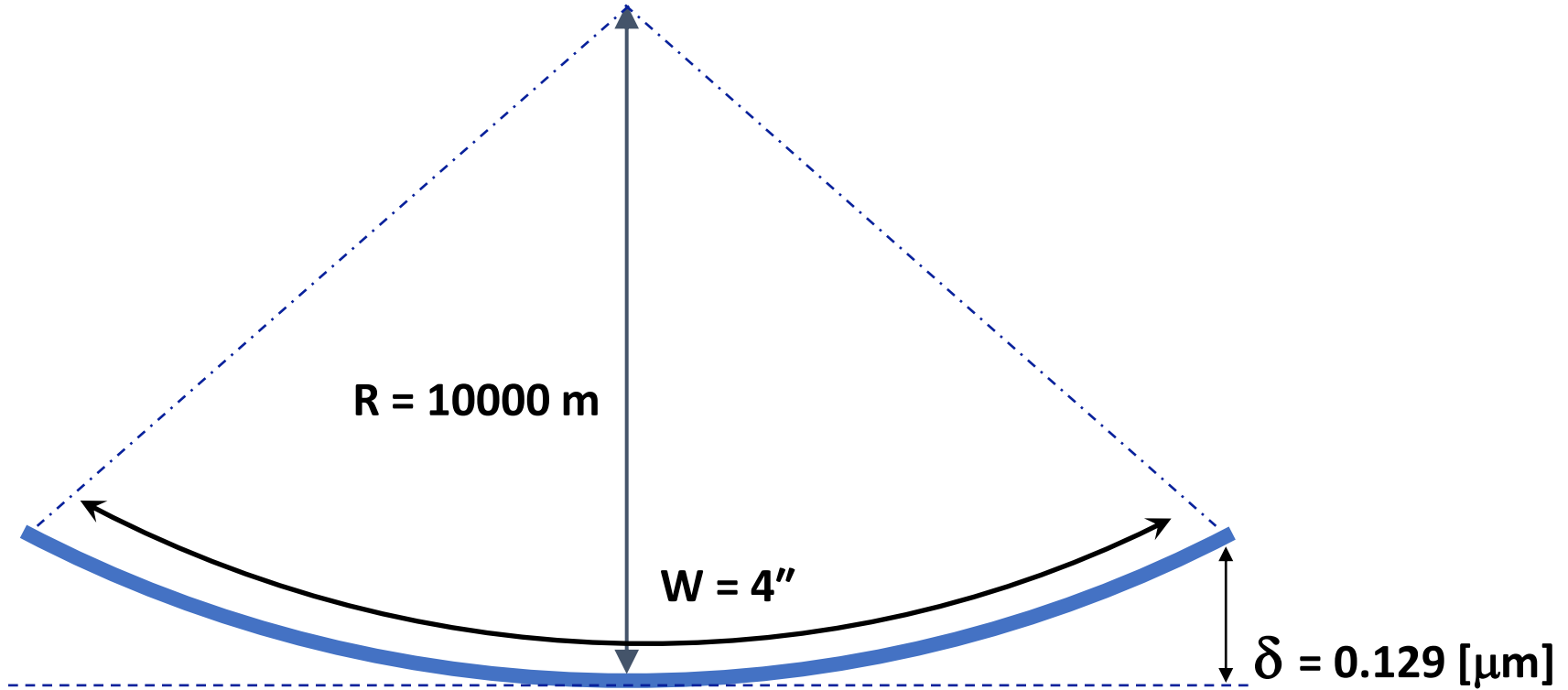
- › Curvature $k = \frac{1}{R}$



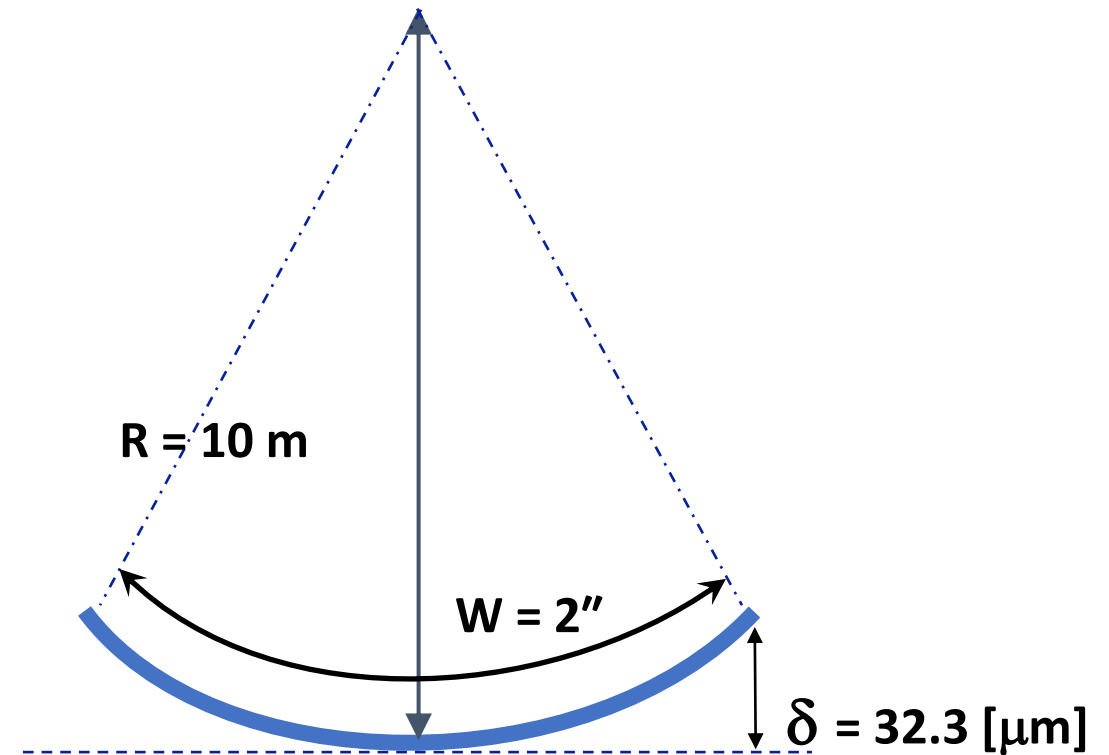
- Curvature $k = 0.1 \text{ [km}^{-1}\text{]}$



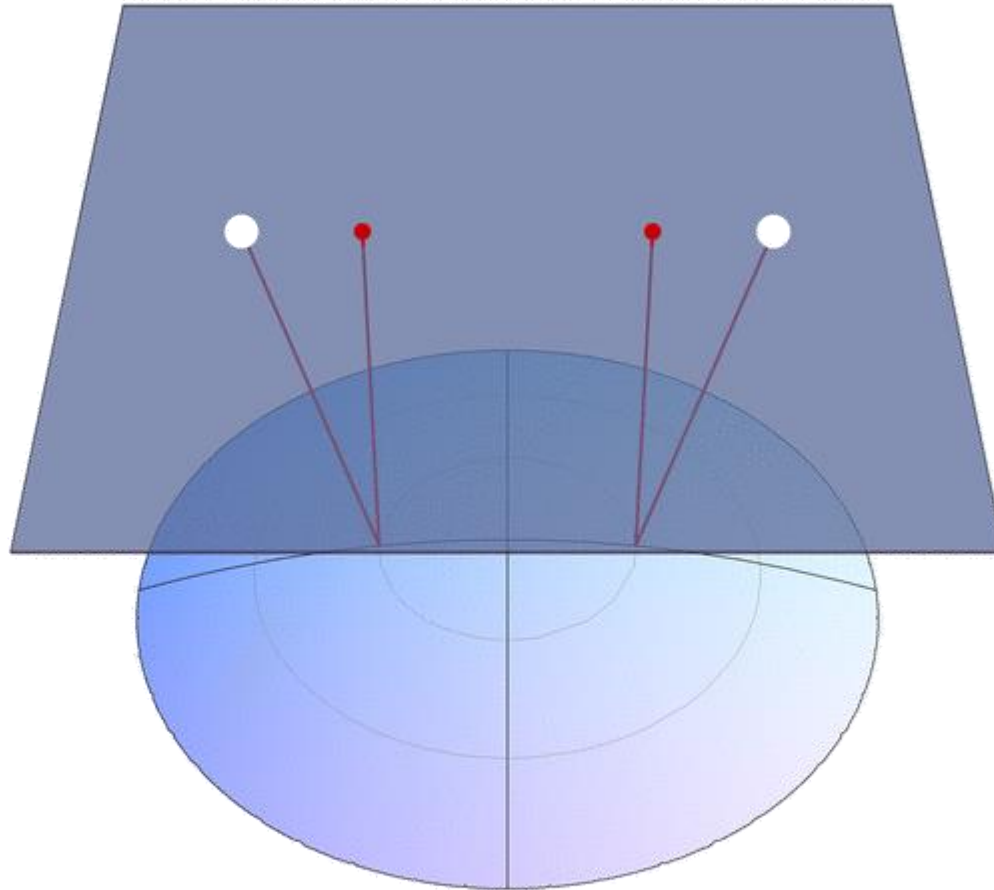
- Curvature $k = 0.1 \text{ [km}^{-1}\text{]}$



- Curvature $k = 100 \text{ [km}^{-1}\text{]}$
- Why does it matter?
 - Temperature uniformity → performance uniformity
 - Avoid cracking
 - Avoid complications further down the chain, e.g in lithography



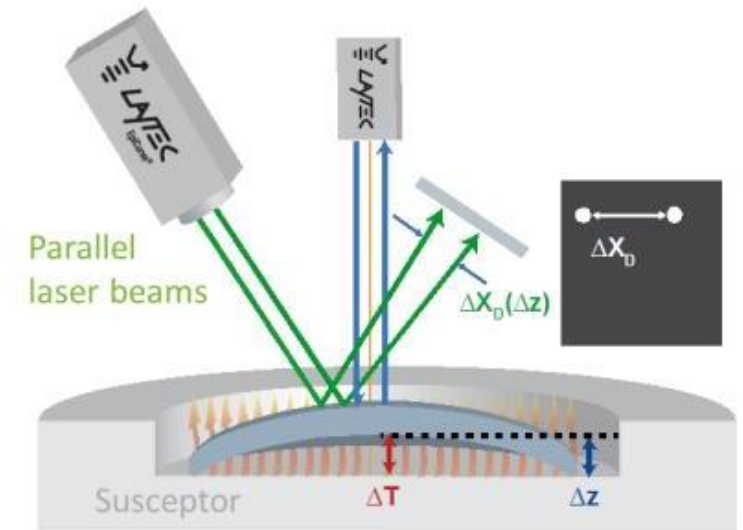
- Incident beam
- Reflected beam



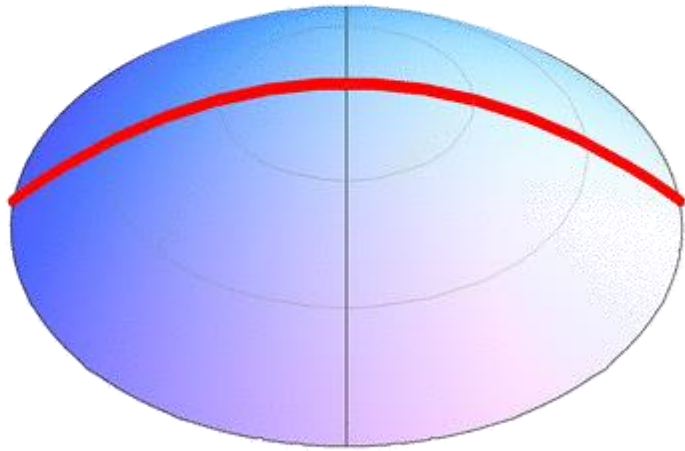
Concave

Flat

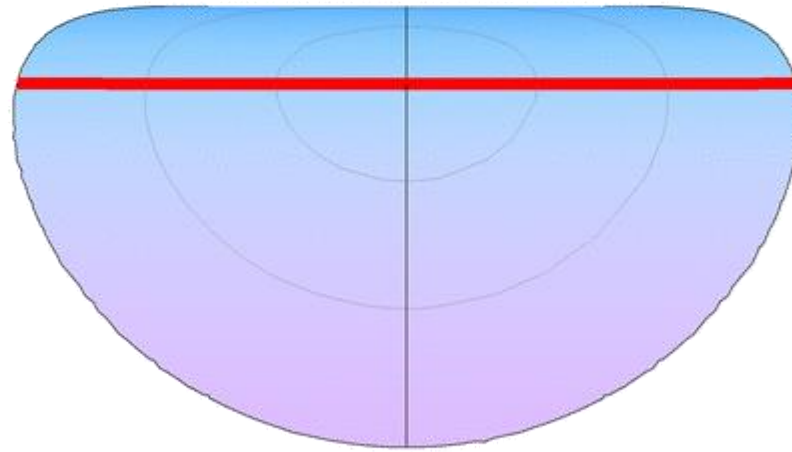
Convex



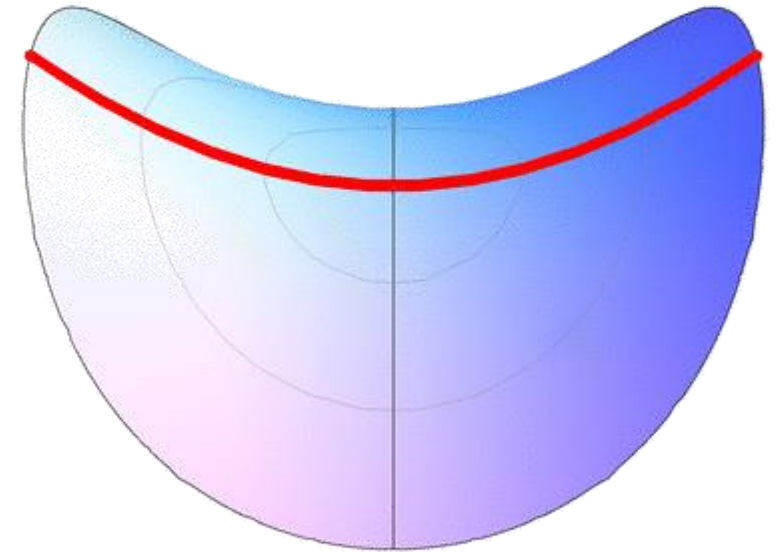
Spherical



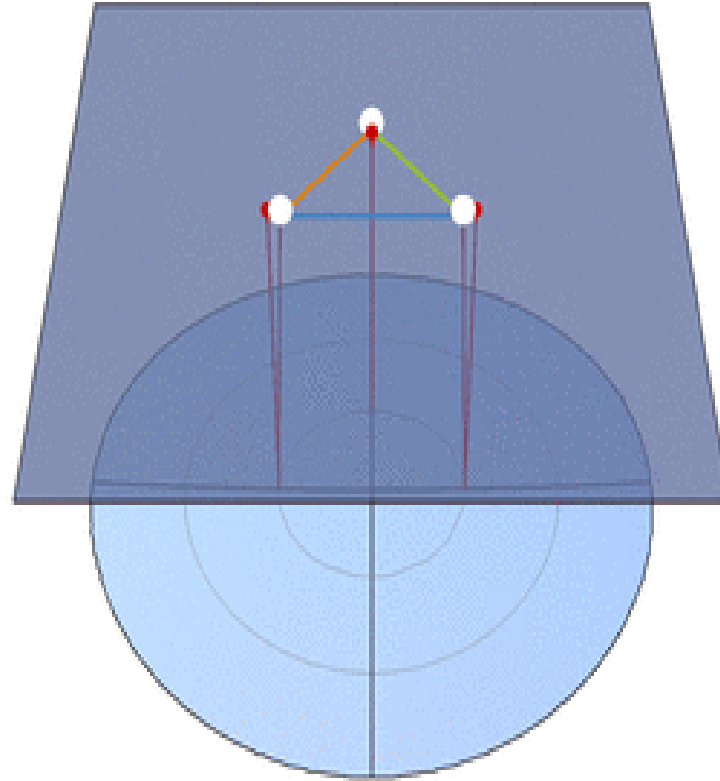
Parabolic



Hyperbolic



Solution: 3-point measurement



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Pyrometry: how does it work?

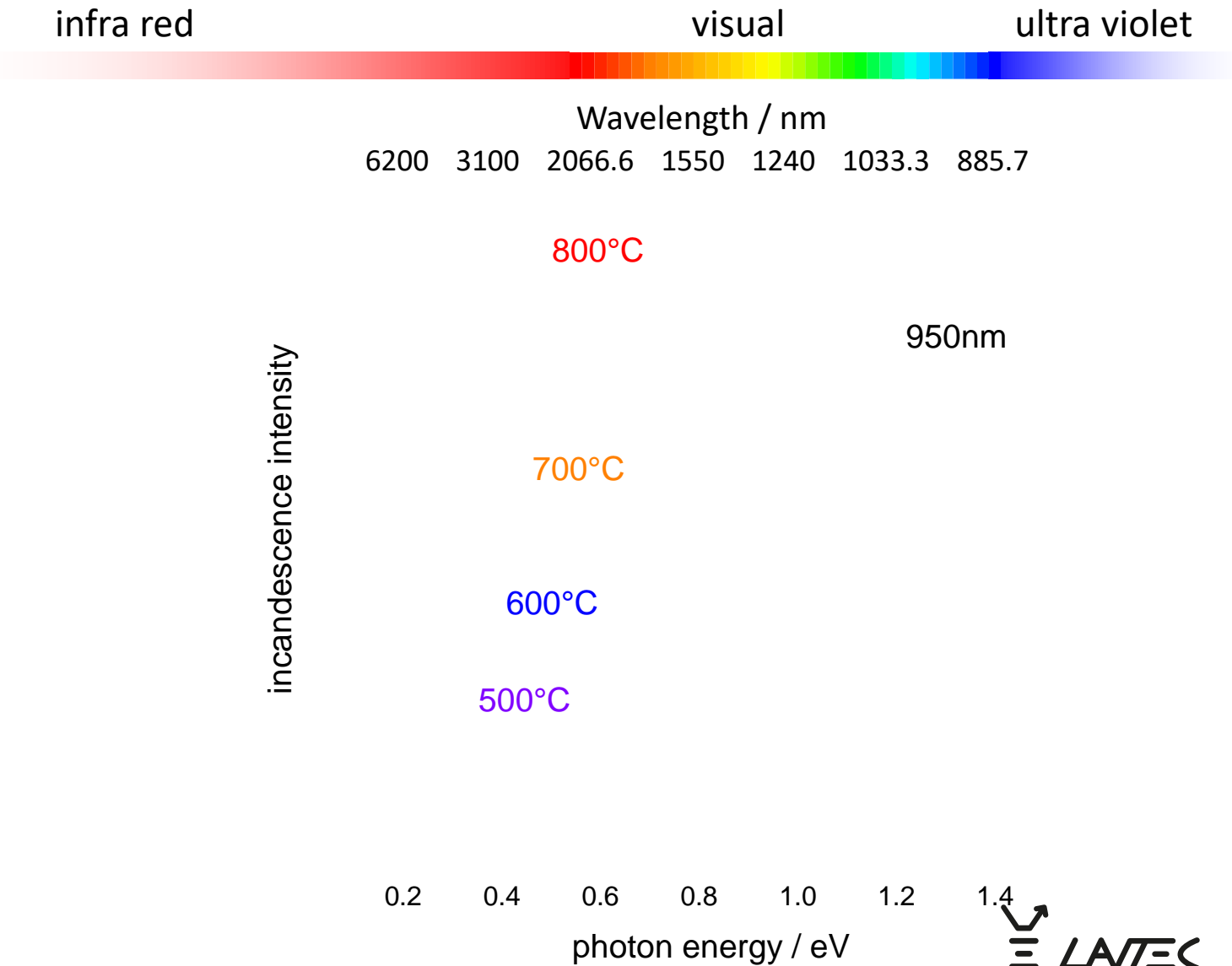
➤ Plank's equation for black body*:

$$I = \frac{2}{h^4 c^3} \cdot \frac{(\hbar\omega)^5}{e^{\hbar\omega/K_B T} - 1}$$

➤ Normal materials:

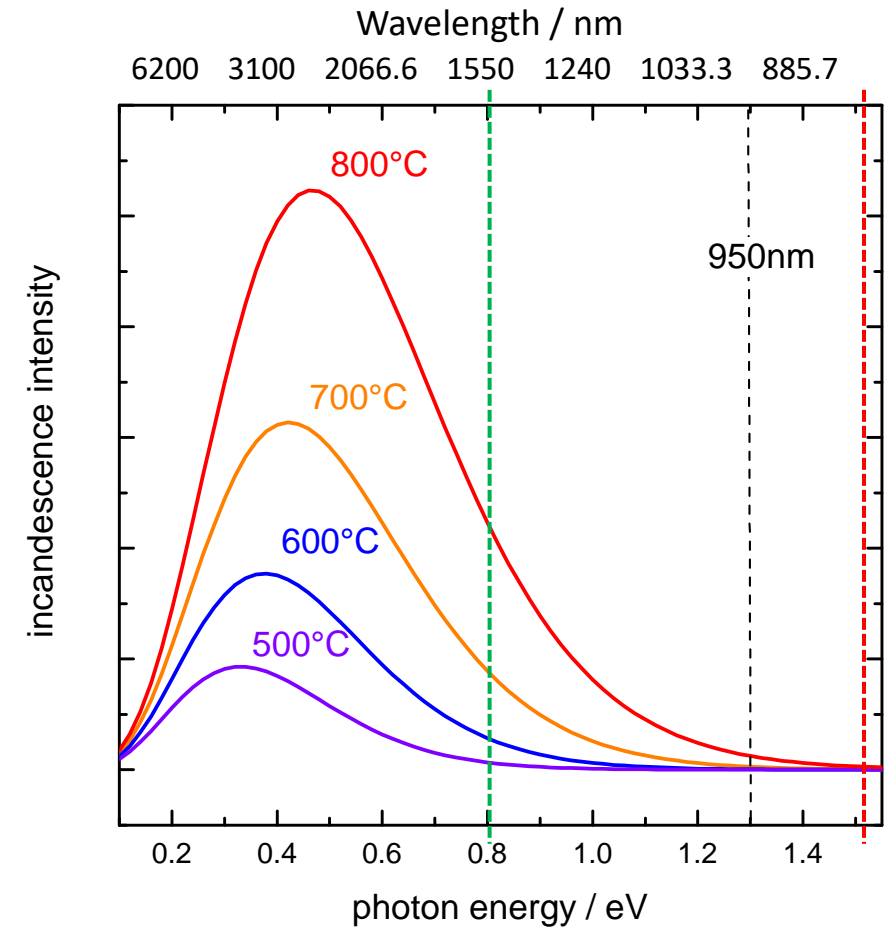
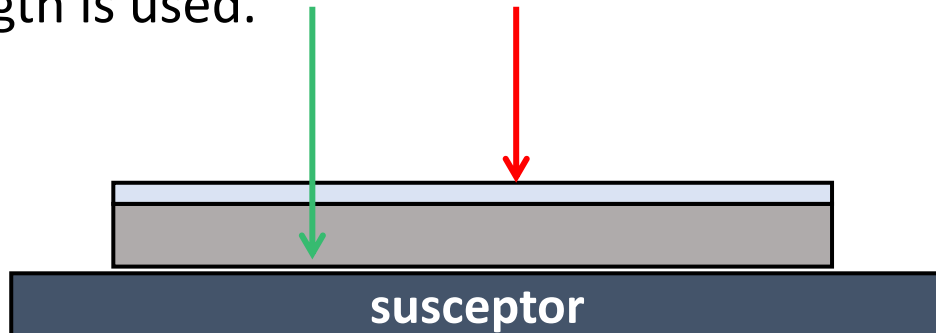
$$I = \epsilon \cdot \frac{2}{h^4 c^3} \cdot \frac{(\hbar\omega)^5}{e^{\hbar\omega/K_B T} - 1}$$

emissivity ↑

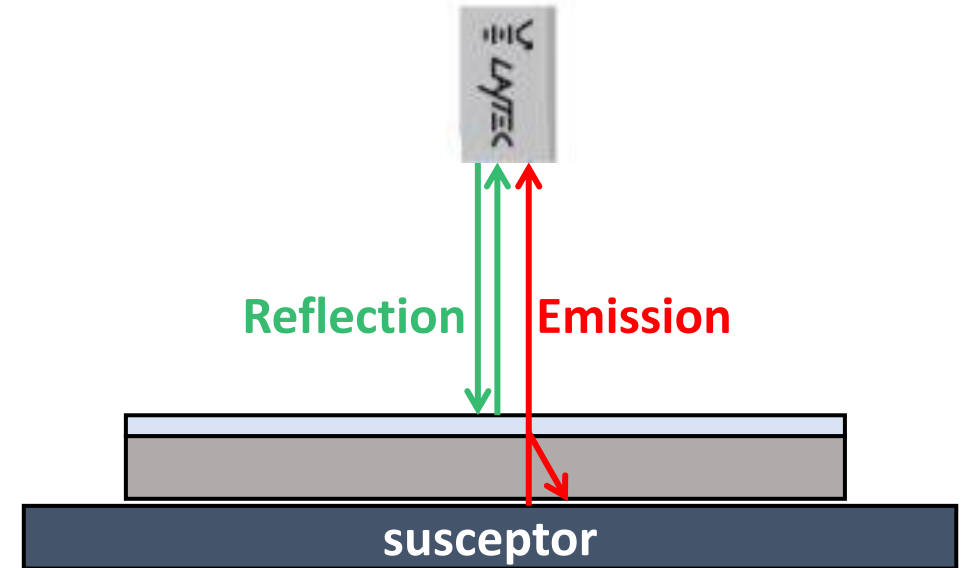
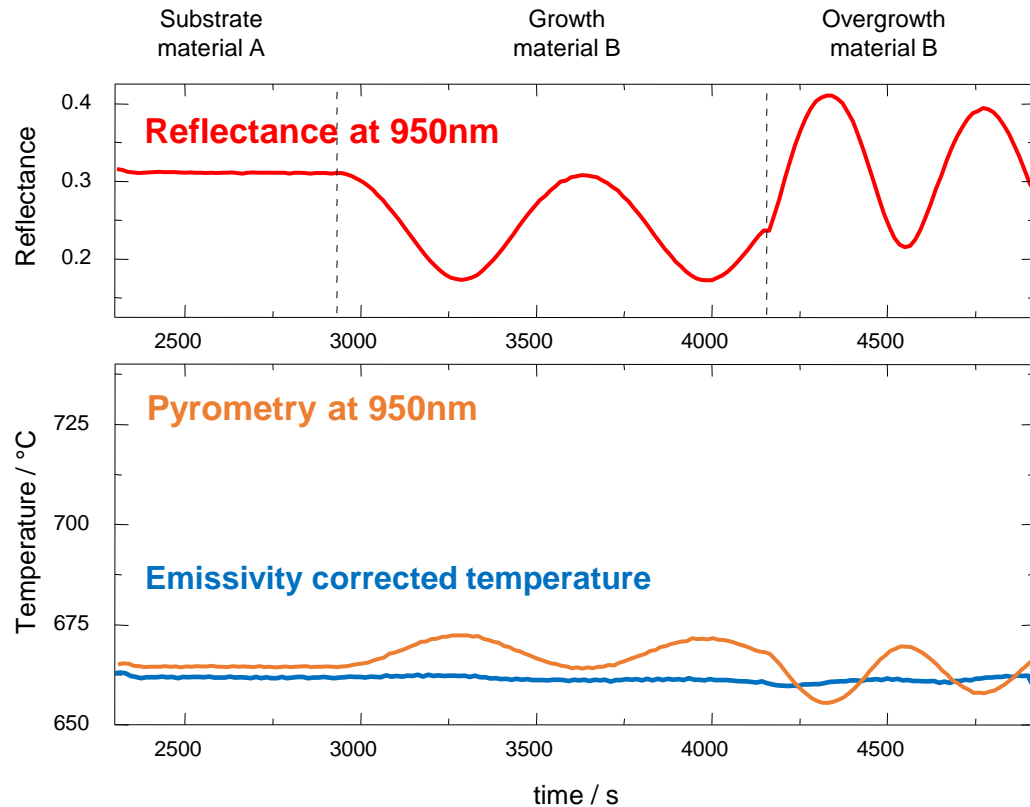


* Planck, Max. "The theory of heat radiation." Entropie 144.190 (1900): 164.

- Epitaxy deals with **surface** chemistry.
- Lower photon energies → transparency regime → susceptor temperature.
- Higher energies → not enough intensity
- 950 nm best choice for most applications
- For transparent substrates (SiC), even shorter wavelength is used.



- › Conservation of energy
 - › $\alpha + r + t = 1$
 - › Opaque semiconductor: $\alpha + r = 1$
- › Kirchhoff's law: $\alpha(\lambda, T) = \varepsilon(\lambda, T) \rightarrow \varepsilon = 1 - r$



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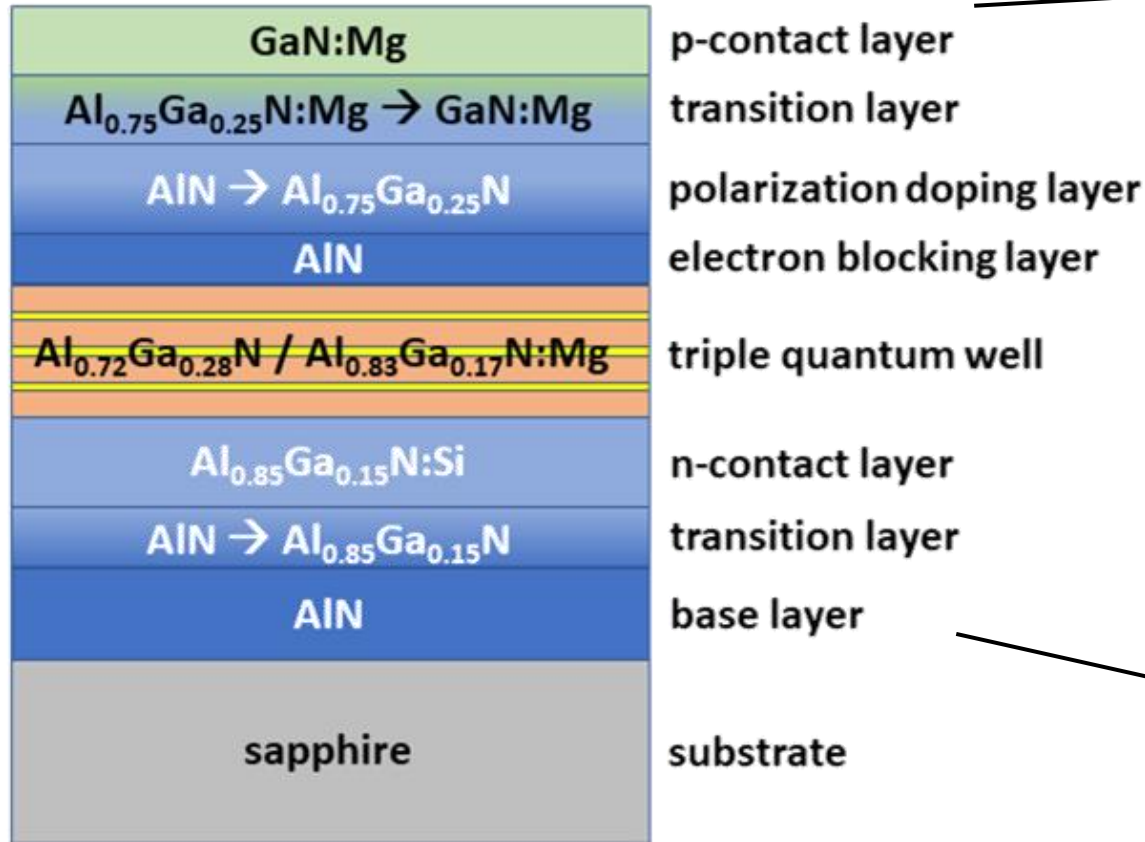
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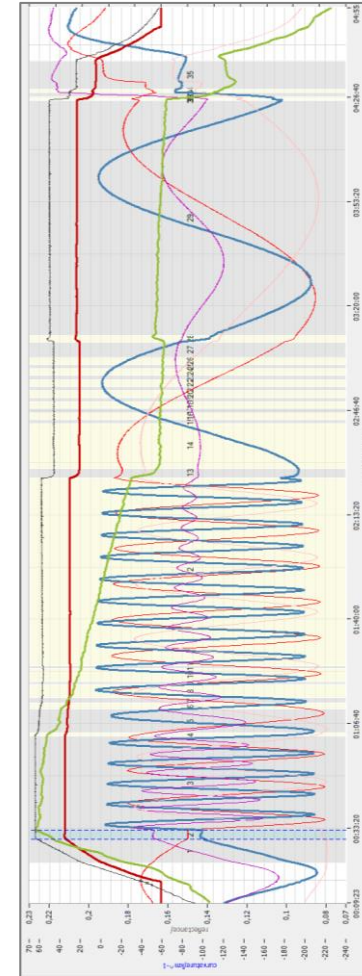
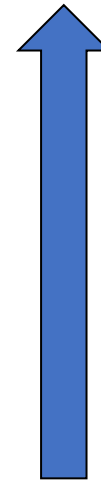
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Schematic layer stack of UV-LED



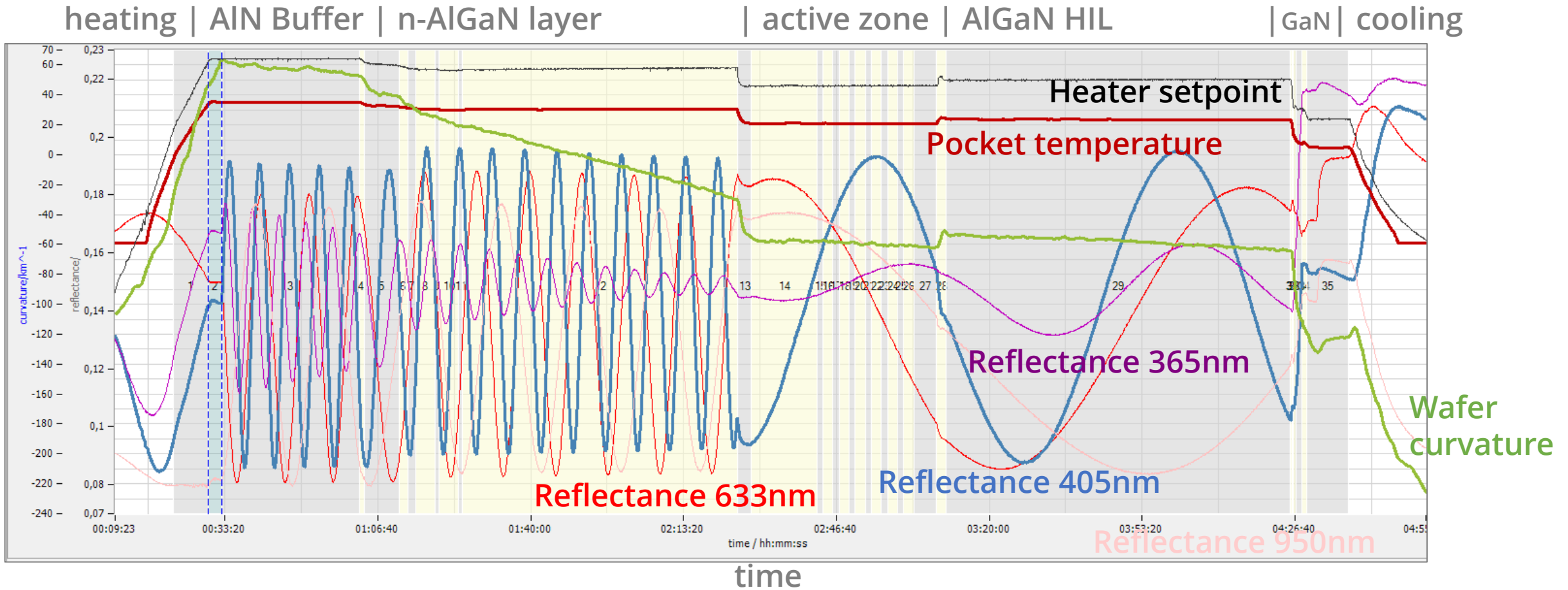
Growth time



In-situ data

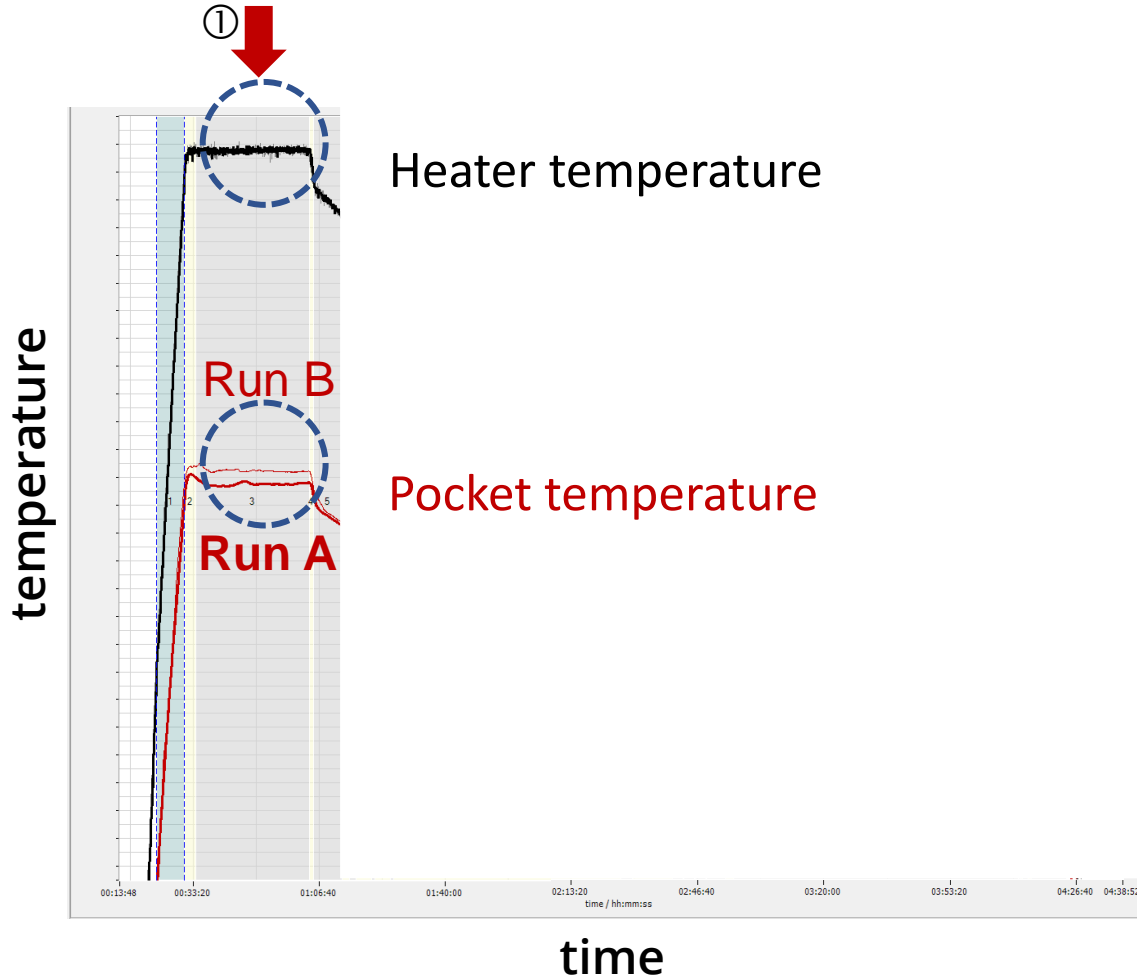
In-situ data of 230 nm UV LED (wafer #1, center)

temperature, reflectance, curvature



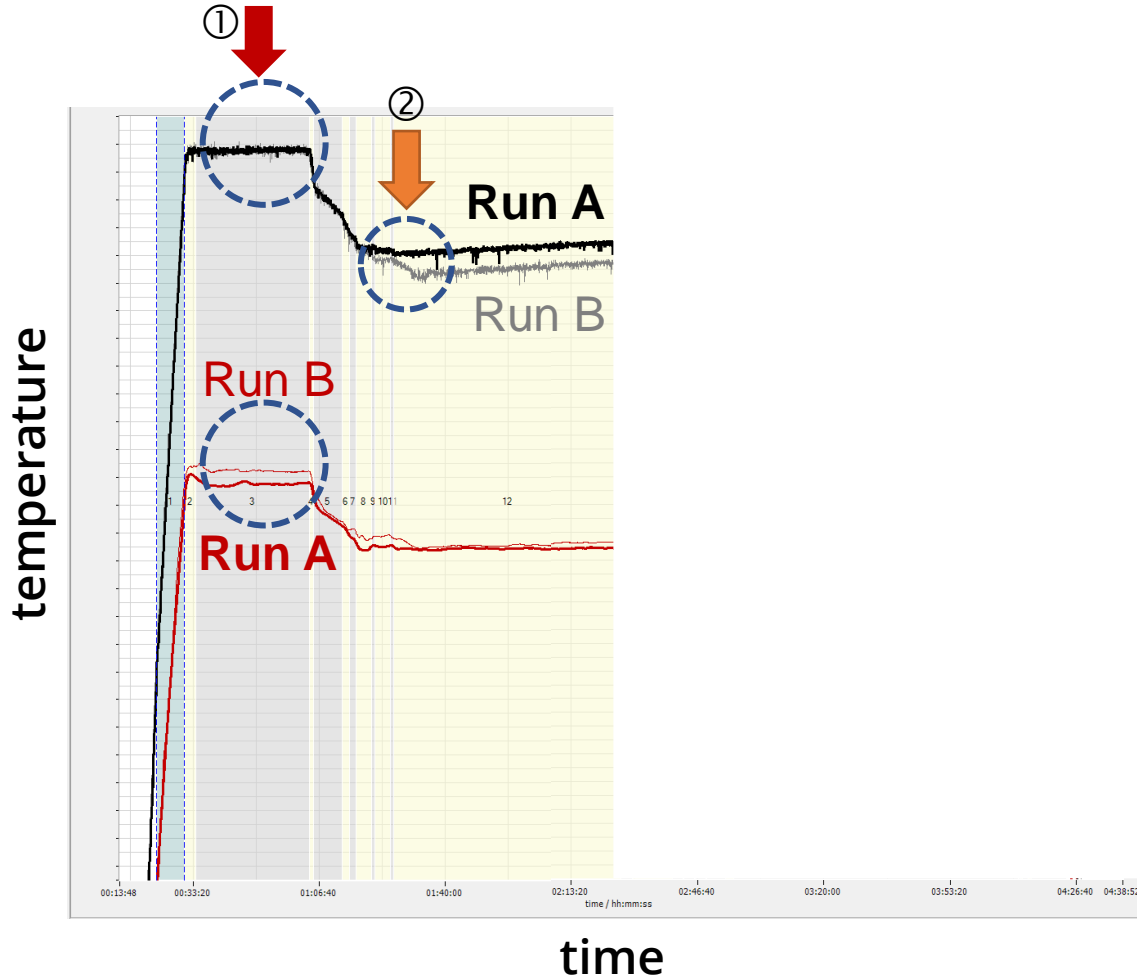
➤ In-situ data: a treasure trove of information about each layer and each wafer

Feed-back control of pocket temperature



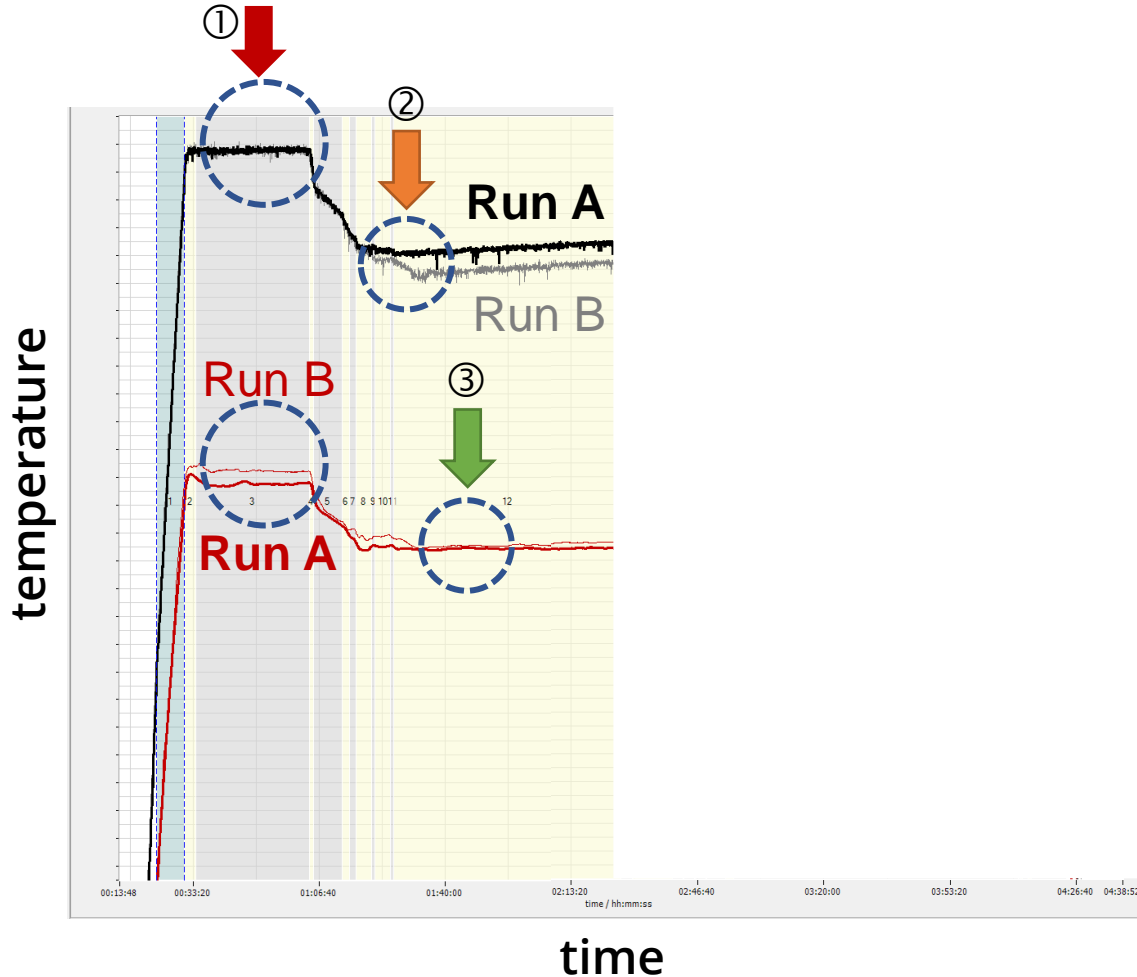
- Run A and B (identical recipe):
- ①: Same heater temperature
- Run B shows higher pocket temperature

Feed-back control of pocket temperature



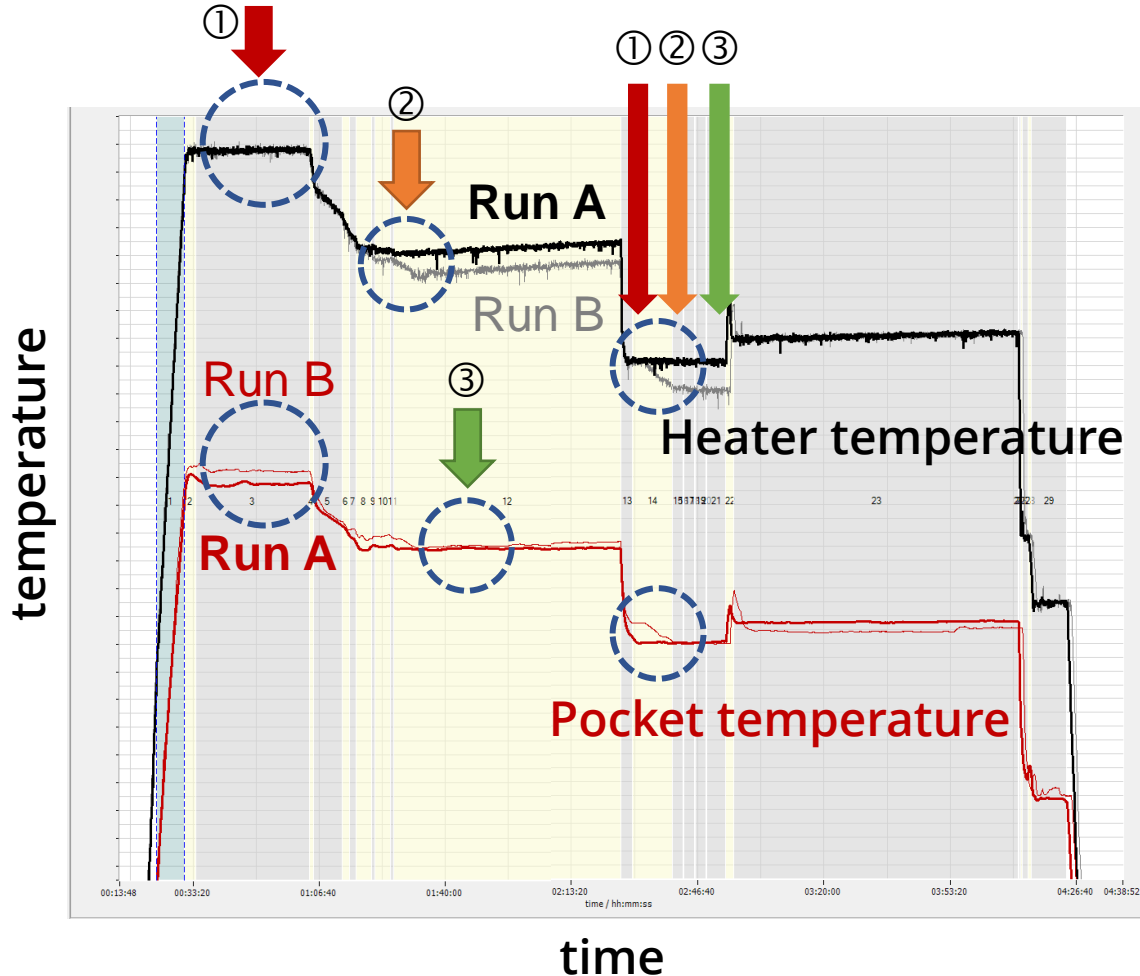
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- ②: Correcting for difference: lowering process temperature in Run B

Feed-back control of pocket temperature



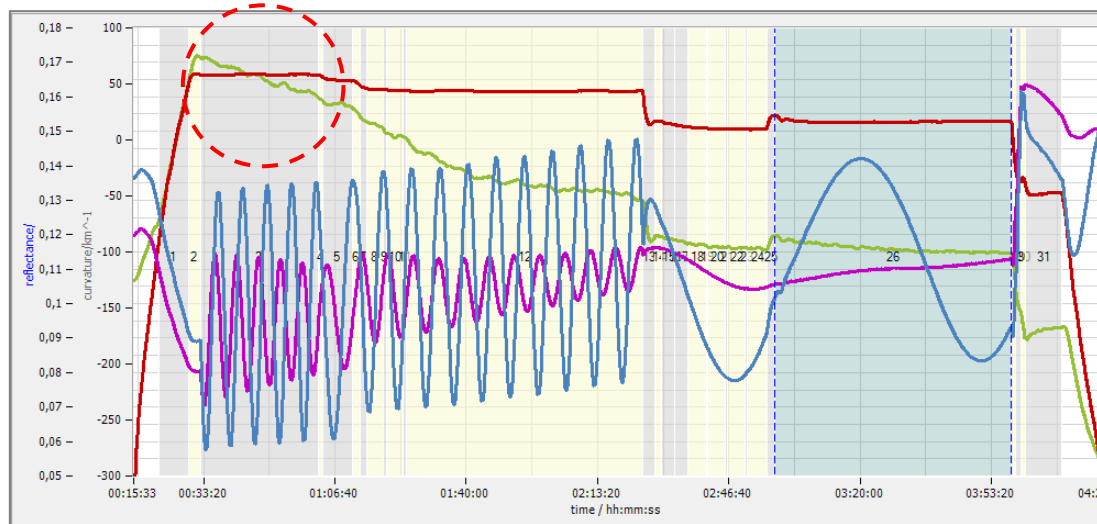
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Feed-back control of pocket temperature

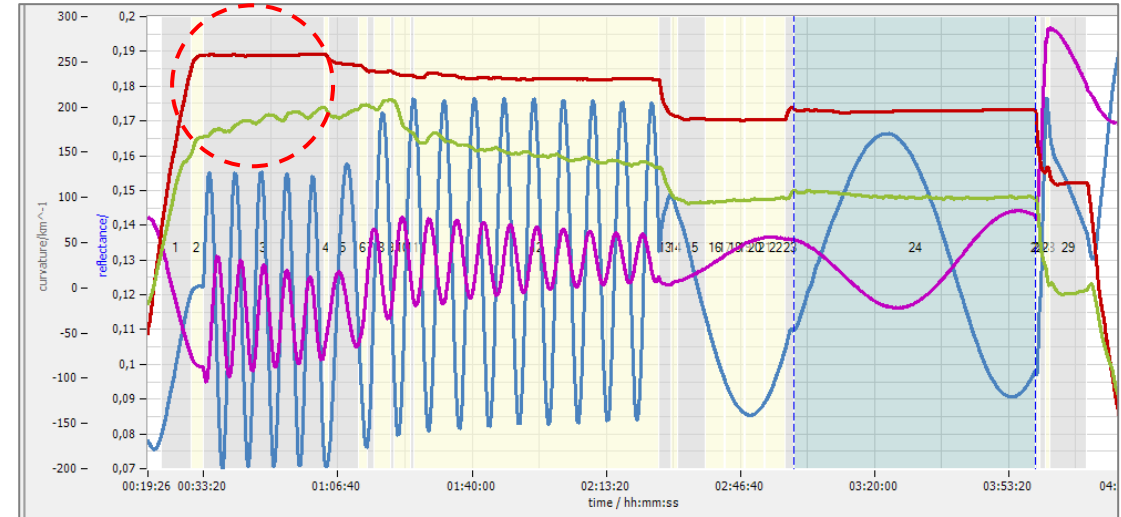


- Run A and B (identical recipe):
- ①: Same heater temperature
- Run B shows higher pocket temperature
- ②: Correcting for difference: lowering process temperature in Run B
- ③: Same pocket temperature established as in Run A
- Same effect in 2nd half of run

Wafer A

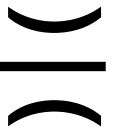
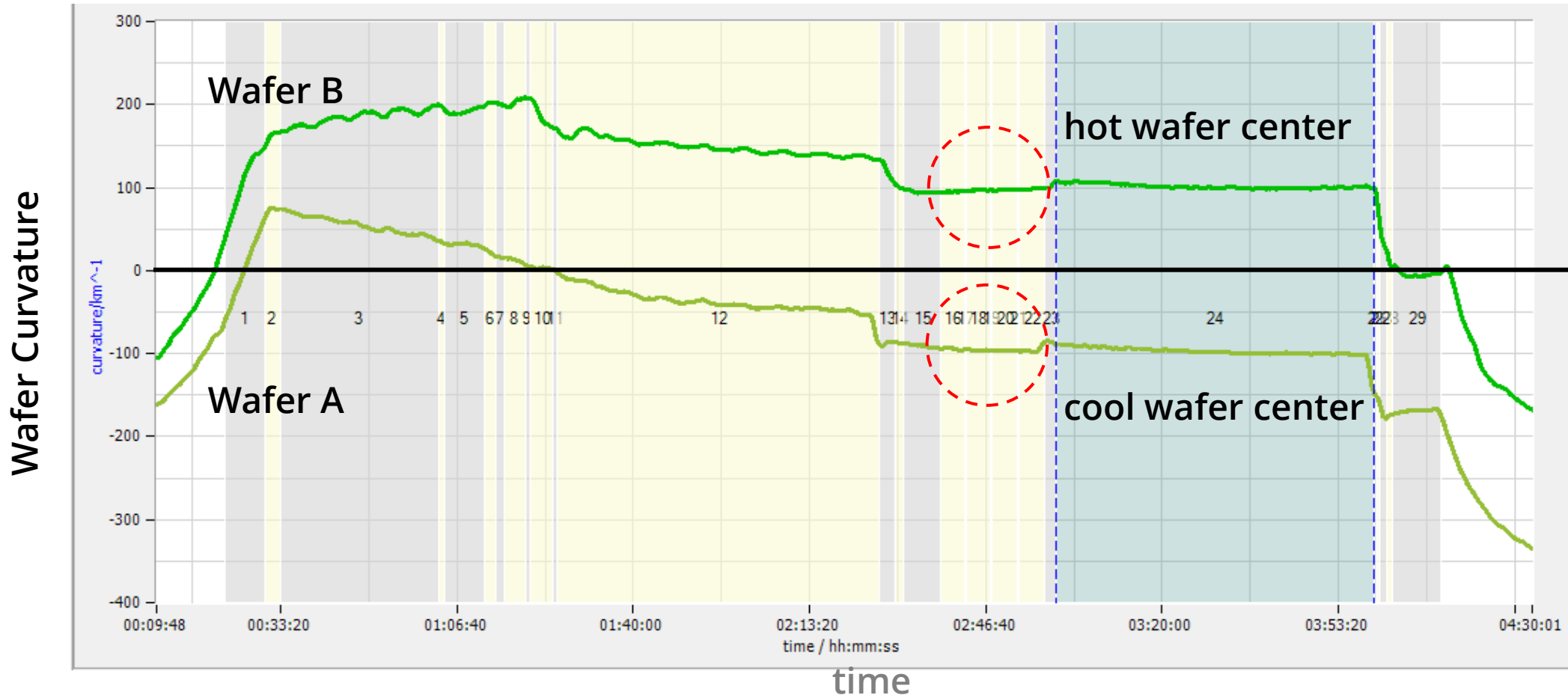


Wafer B



- Two runs with comparable recipe and similar looking in-situ data
- But different template → significantly different strain development during AlN growth
- Result: Strong difference in wafer curvature during growth of MQW

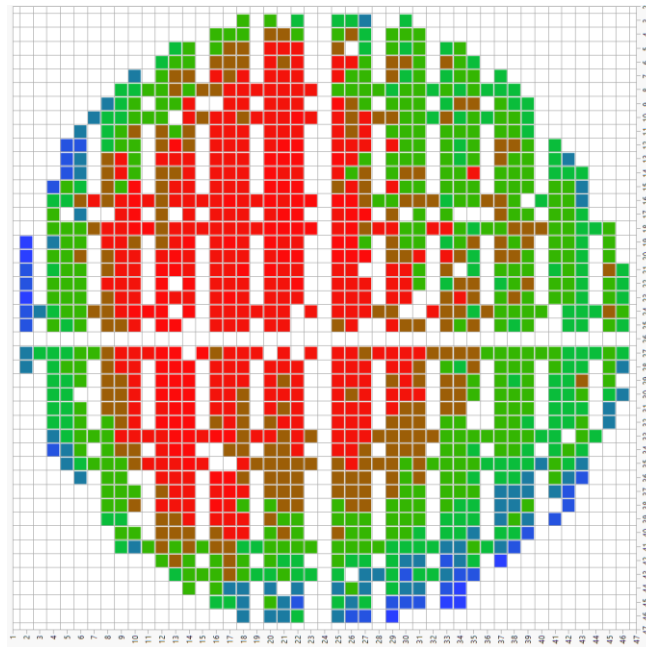
In-situ curvature measurement



➤ Uniformity of LED emission can already be predicted

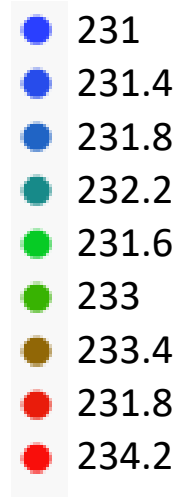
Electroluminescence maps

Wafer A 

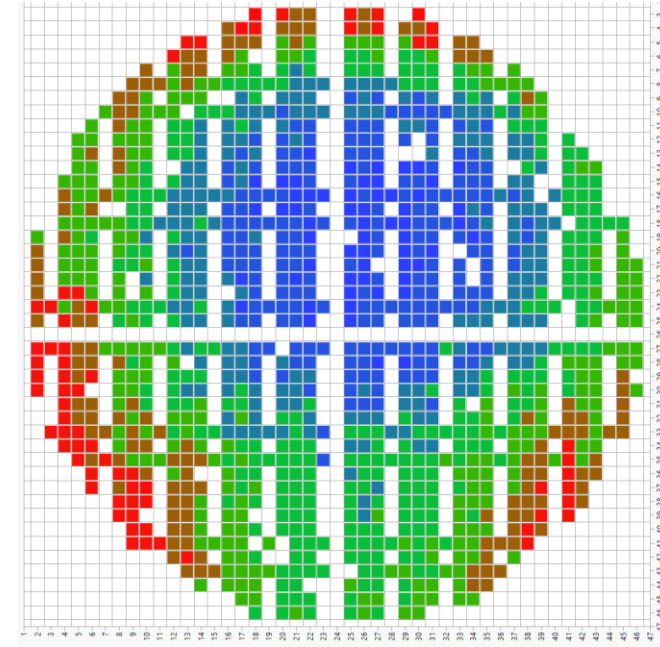


$k_{AZ} = -96 \text{ km}^{-1}$

Peak wavelength [nm]



Wafer B 



$k_{AZ} = 97 \text{ km}^{-1}$

- Far-UVC LED on HTA-AlN/Sapphire template
- Longer emission λ in center

- Far-UVC LED on MOVPE-AlN/Sapphire template
- Shorter emission λ in center

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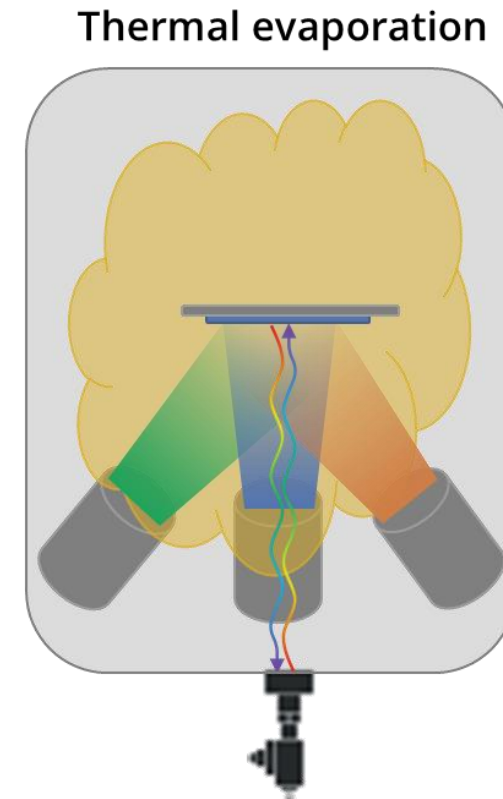
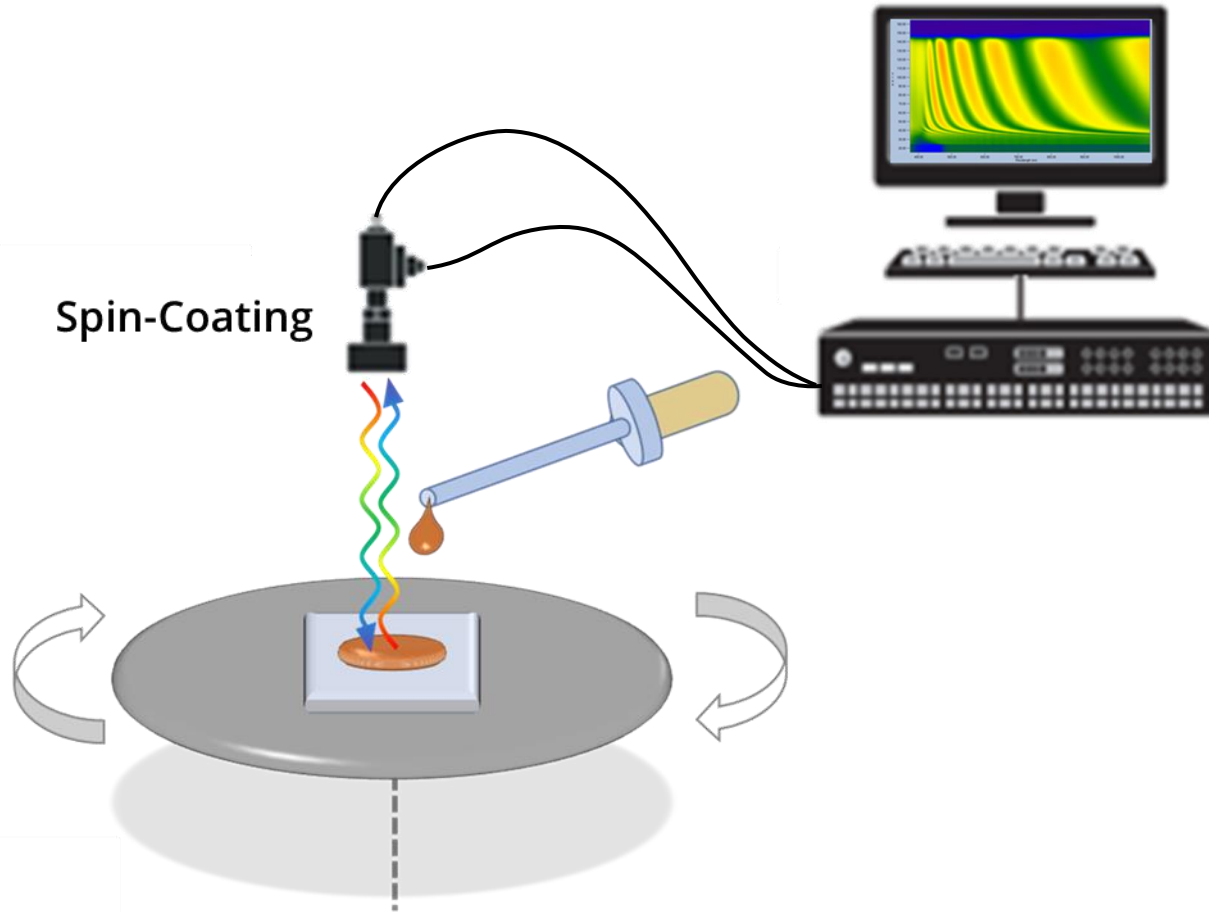
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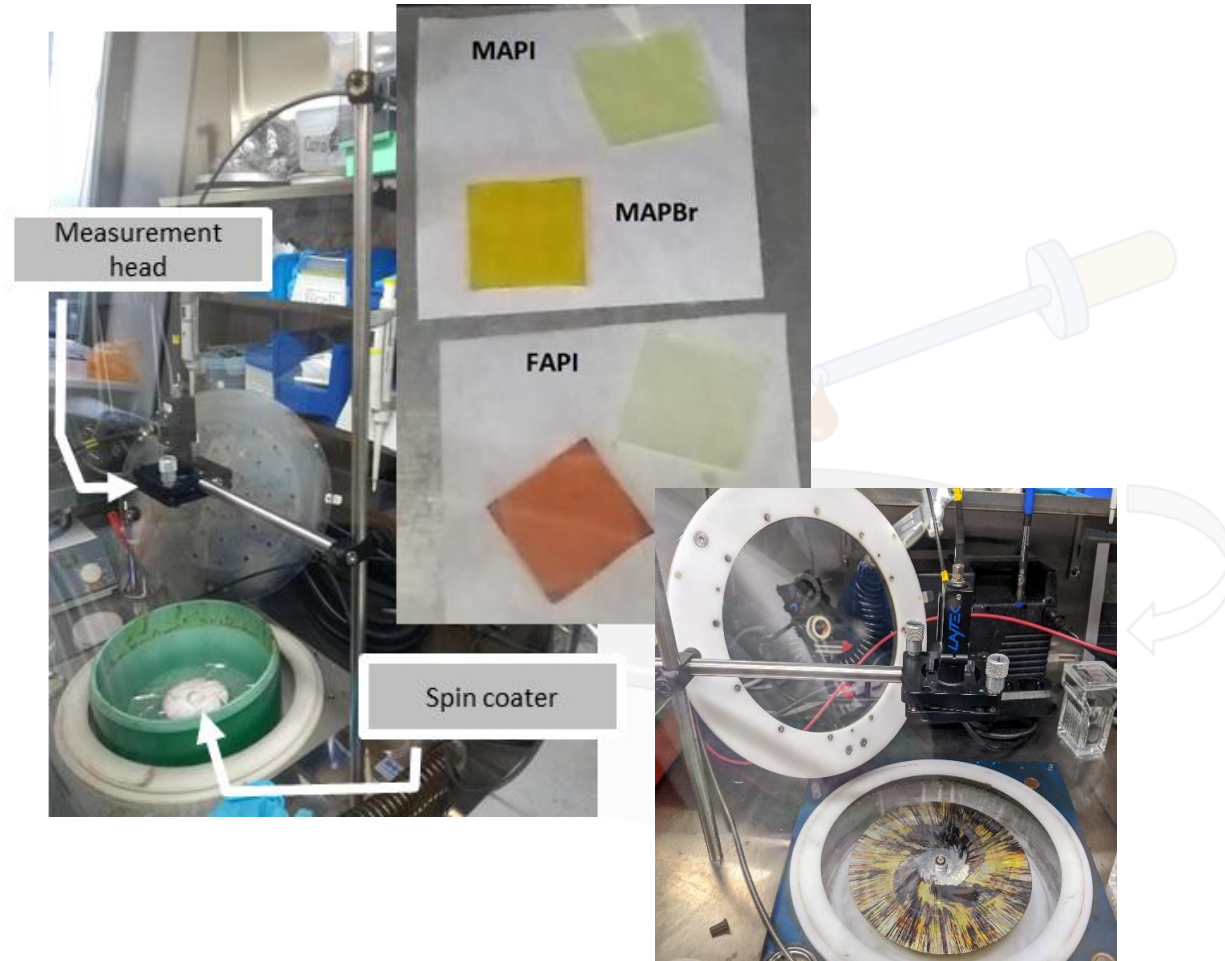
Case study 2, solar cells

Conclusions

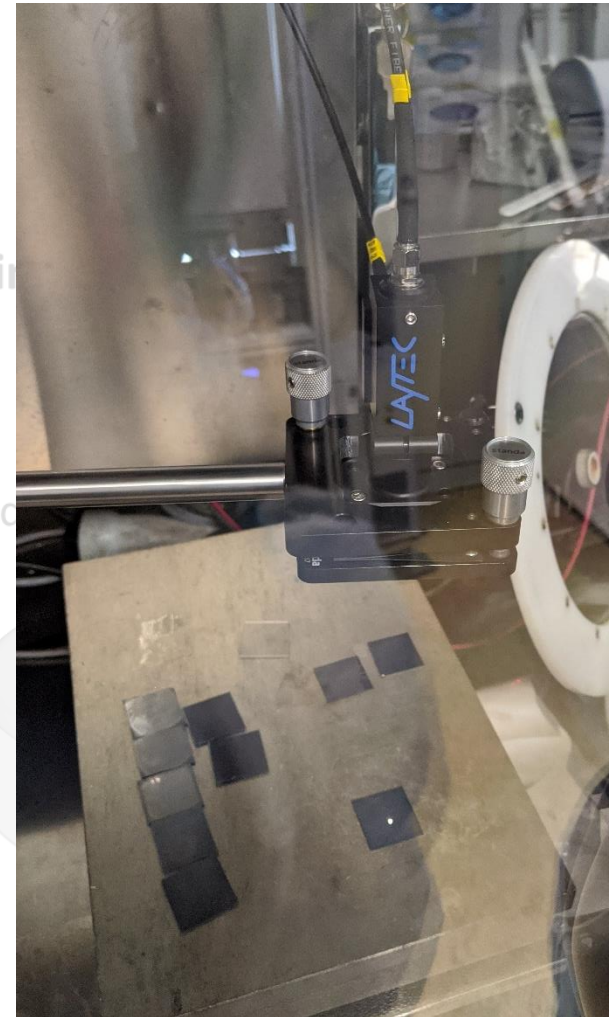
Metrology for high-efficiency photovoltaics: perovskite formation



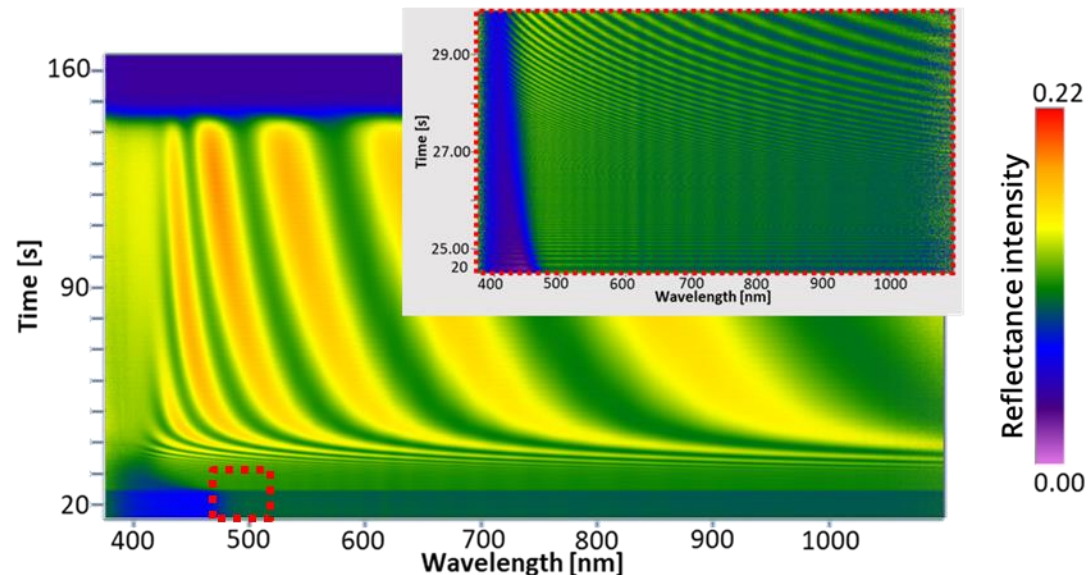
Metrology for high-efficiency photovoltaics: perovskite formation



Annealing

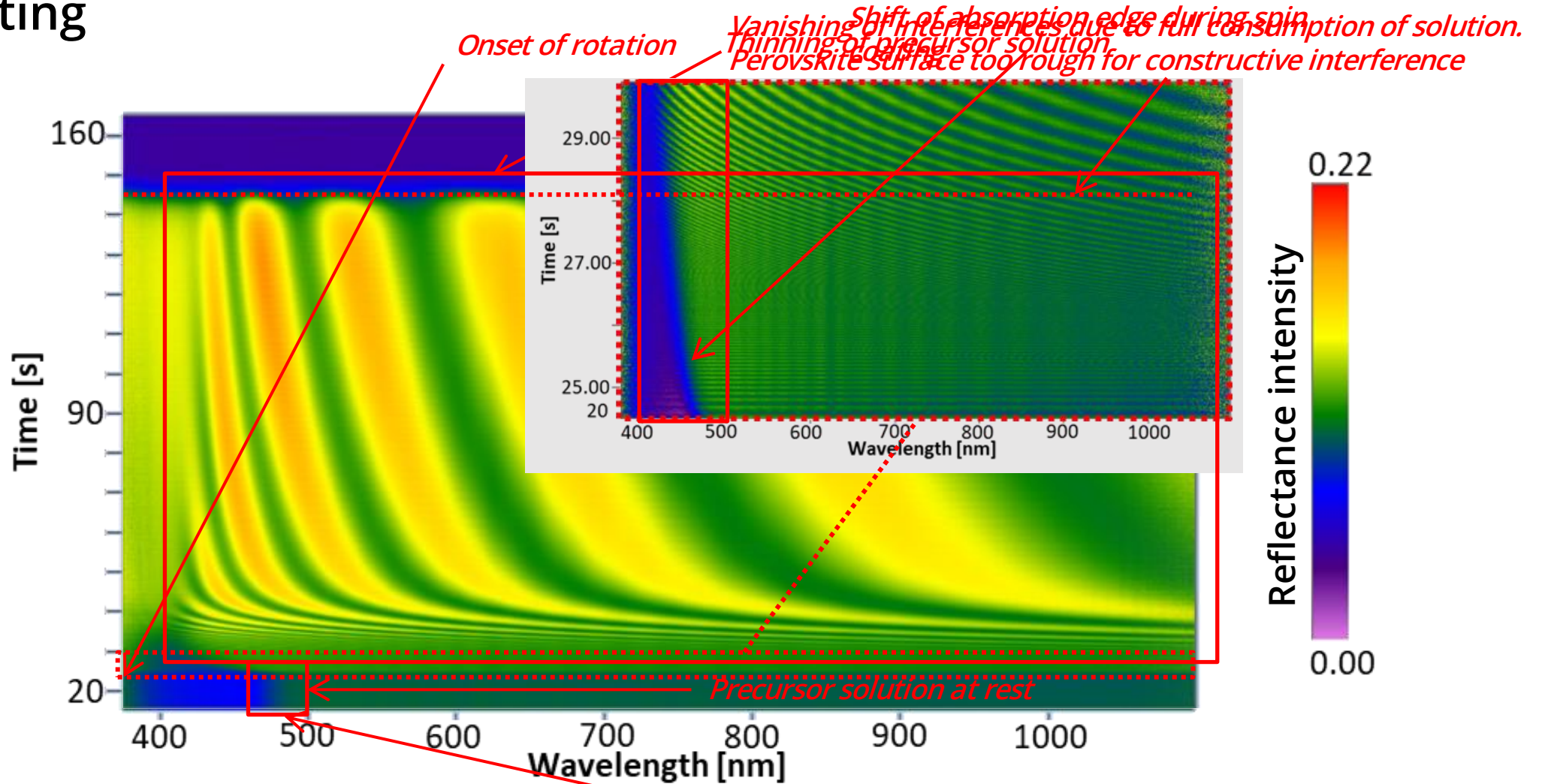


➤ ... during spin-coating



3CAT, Triple Cation Complex; Spin Coating @ 4000RPM; 180s

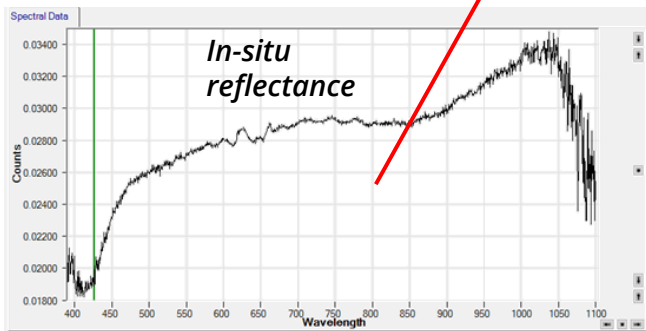
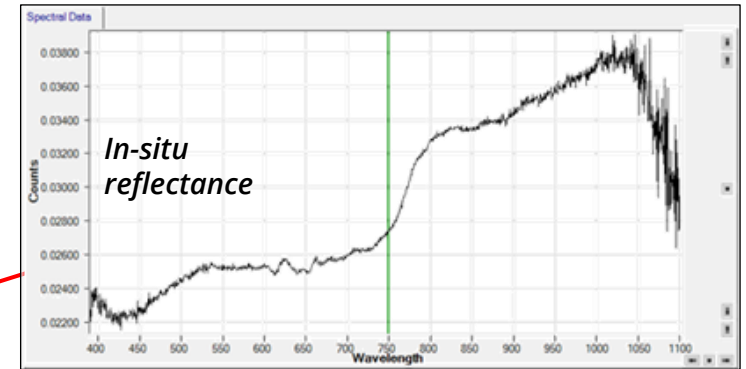
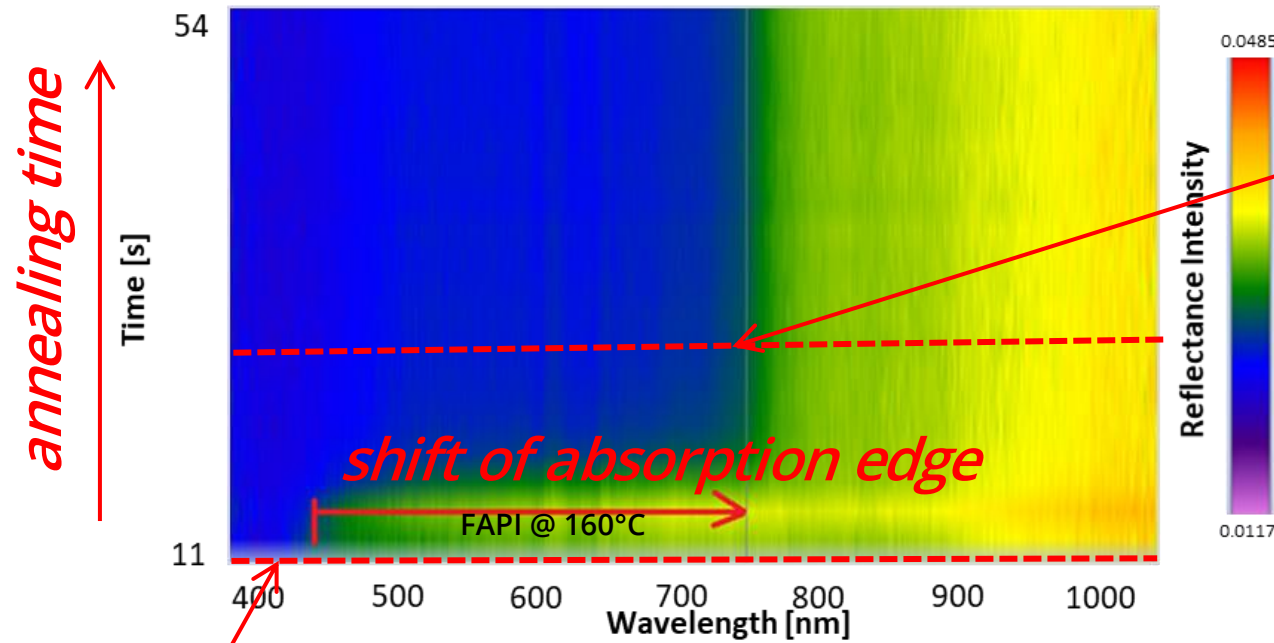
Spin-coating



3CAT, Triple Cation Complex; Spin Coating @ 4000RPM; 180s

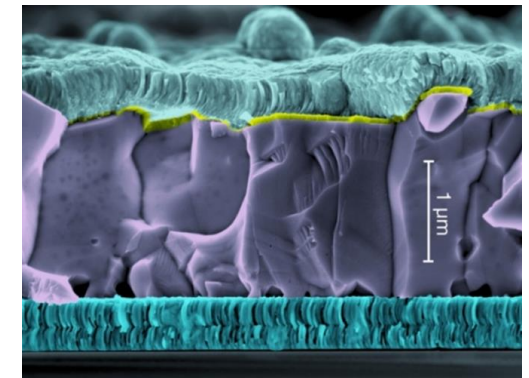
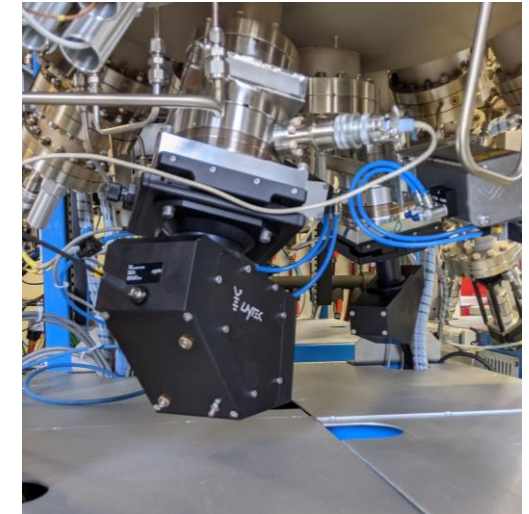
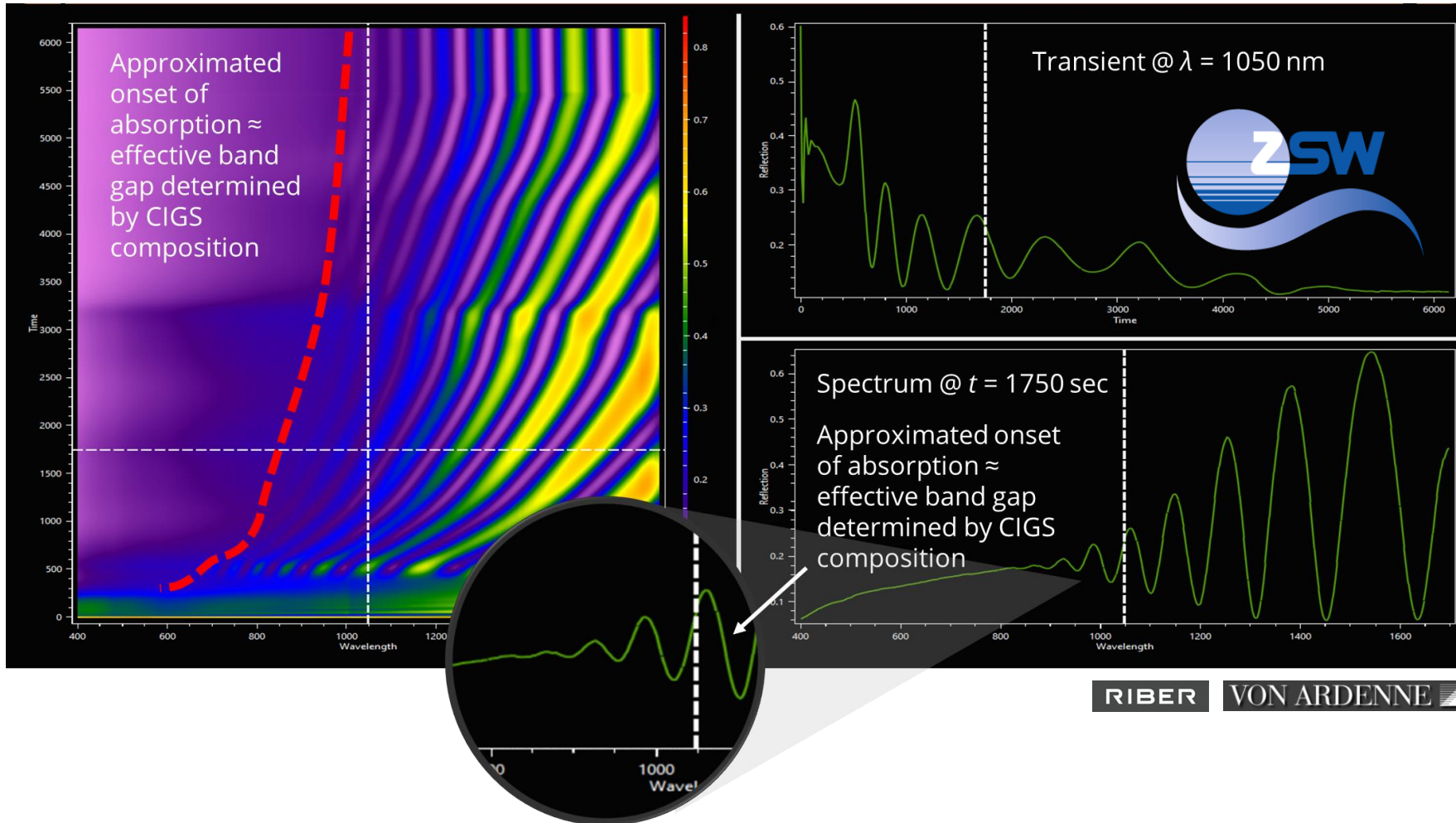
Initial absorption edge of solution

Annealing



Band gap shifts from ~450nm to 725 during annealing.

Metrology for high-efficiency photovoltaics: CIGS bandgap



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Who are we?

History, markets, approach

Light \leftrightarrow Electricity

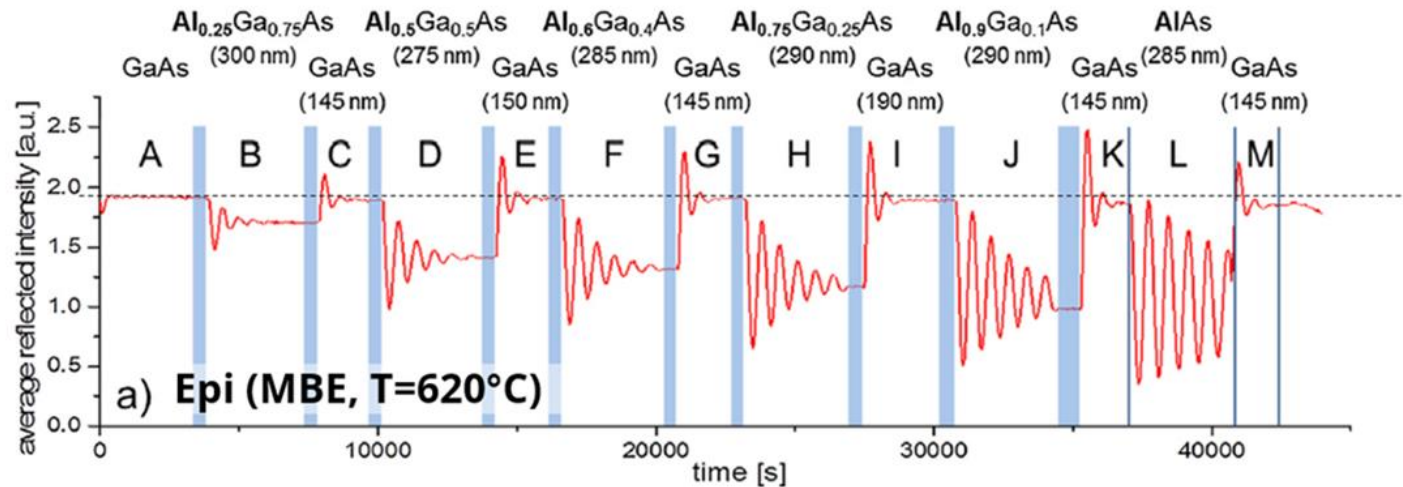
LEDs, Solar cells and transistors

Reflectometry, deflectometry and pyrometry

Case study 3, high power transistor

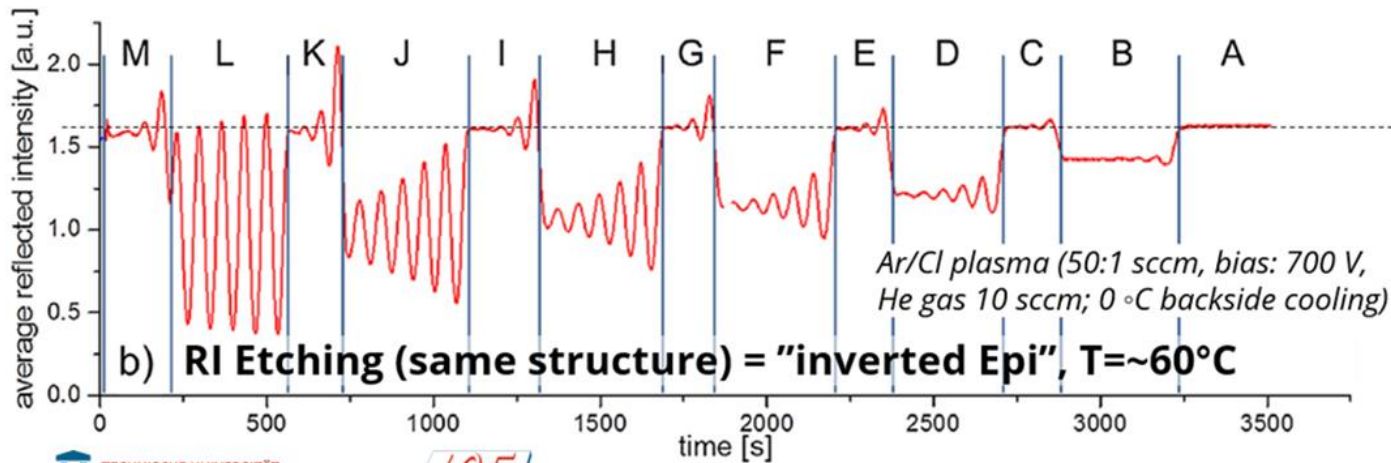
Conclusions

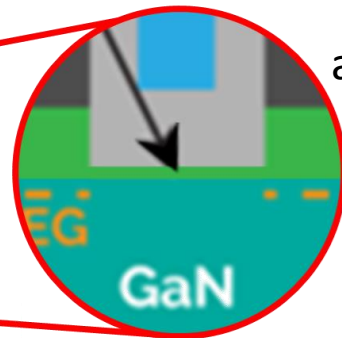
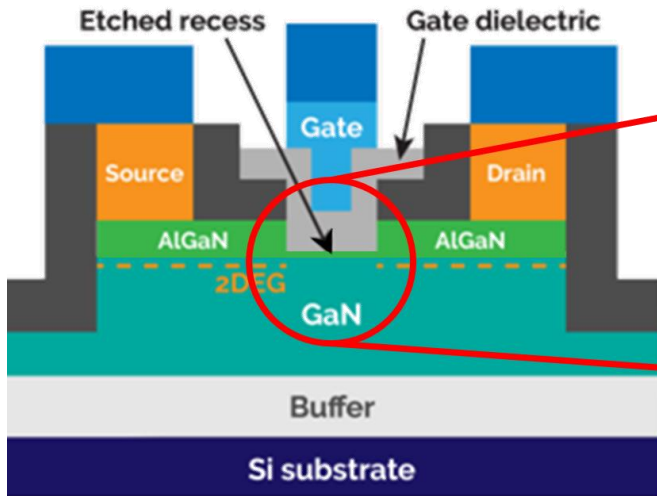
MBE



- Interpreting etching as “inverted epitaxy”
- End point detection possible using interface signatures.

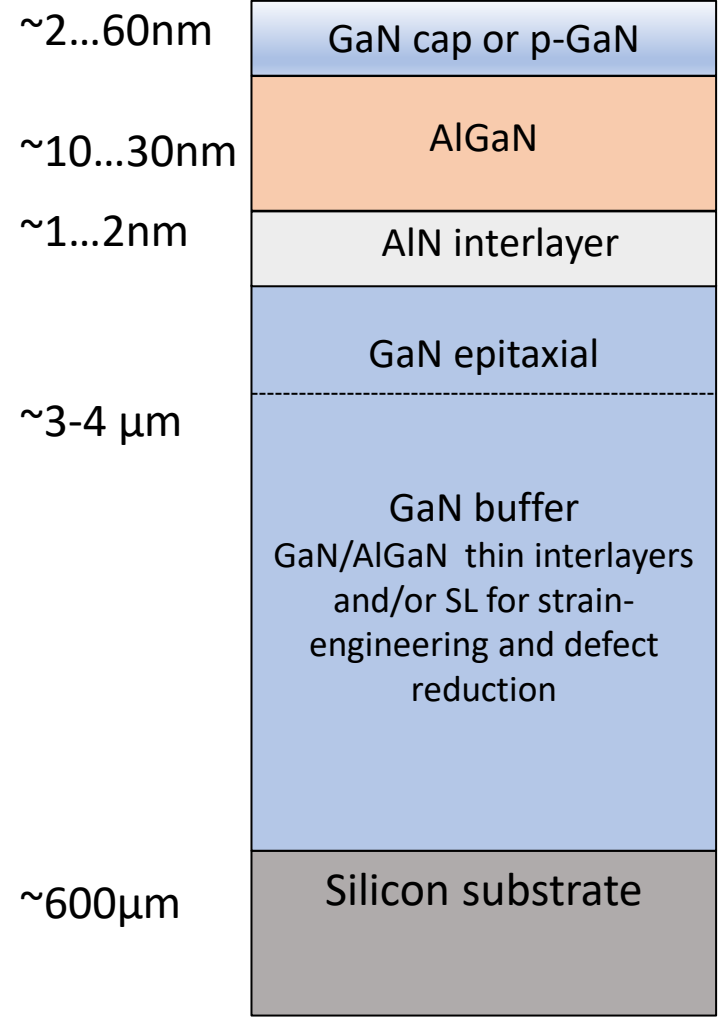
Etch





active region

Typical (simplified) GaN/Si HEMT layer structure

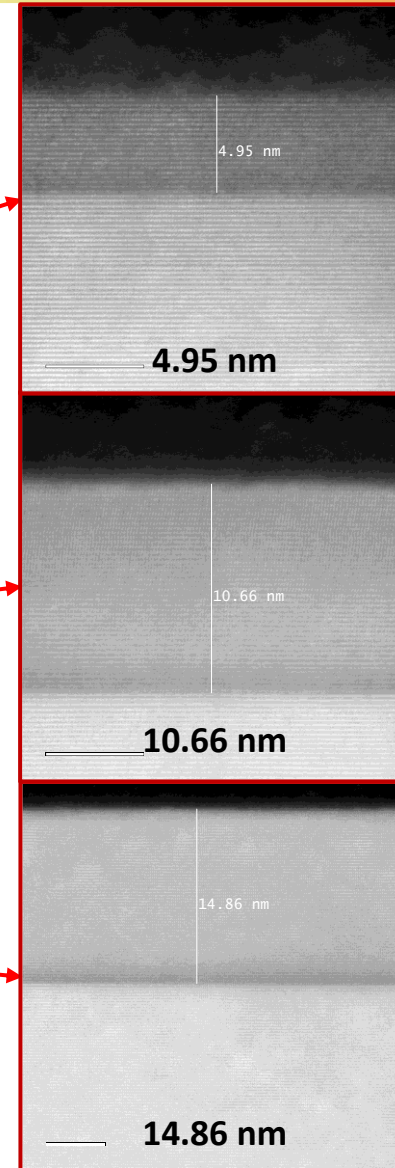
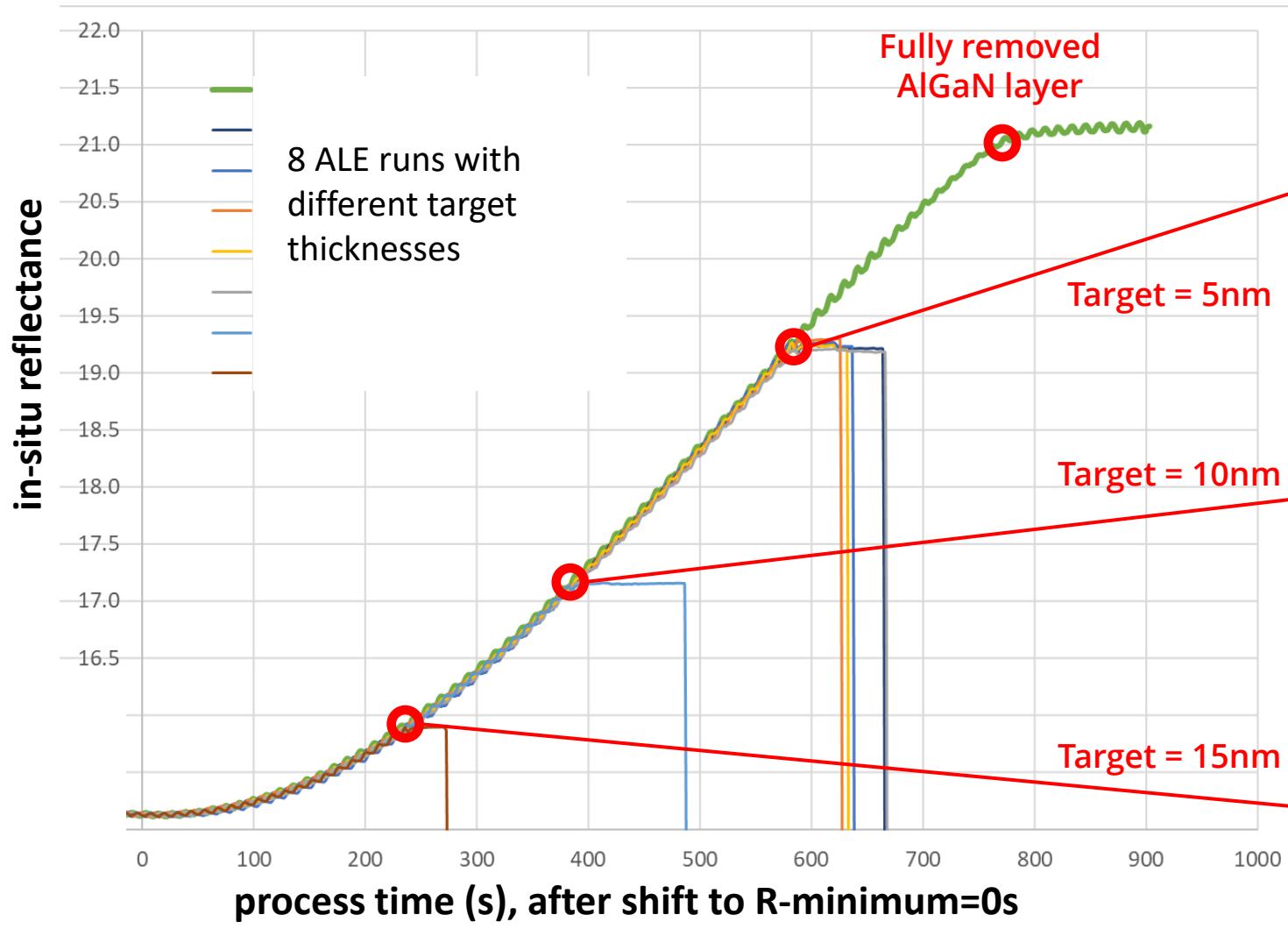


- Atomic layer etching into AlGaN layer
- Target (remaining) thickness: 5, 10 and 15 nm



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Etching monitoring: GaN/Si HEMT (high electron mobility transistor)



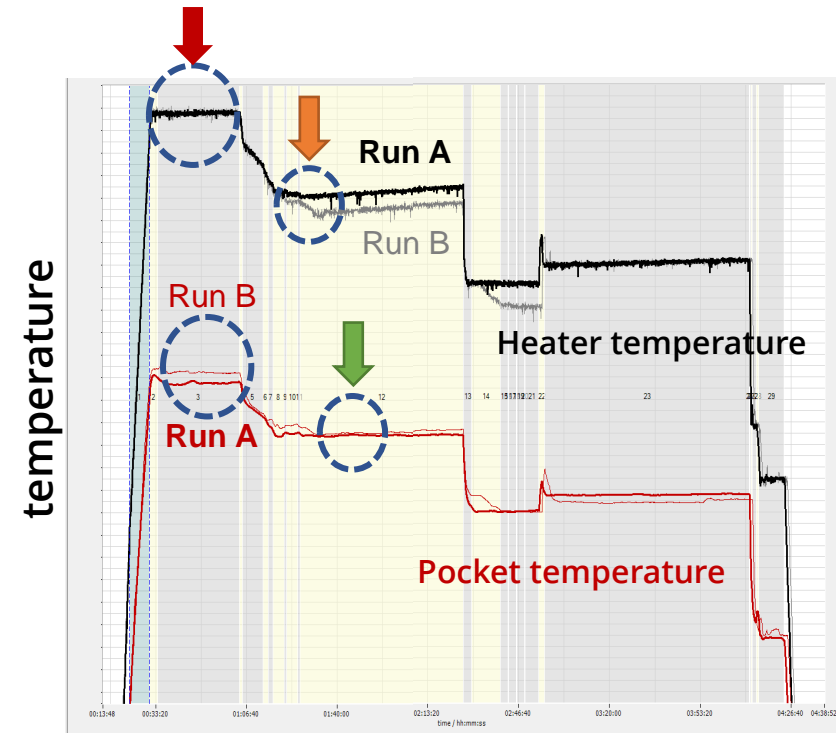
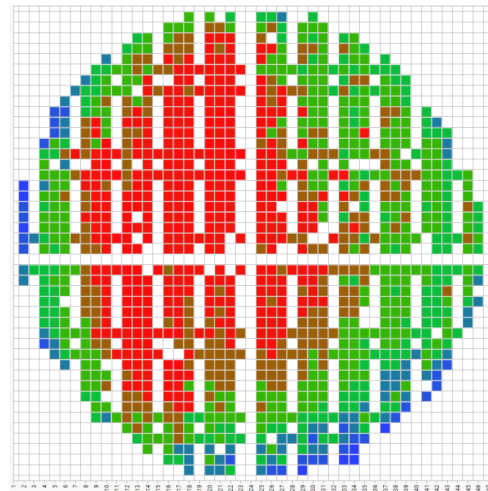
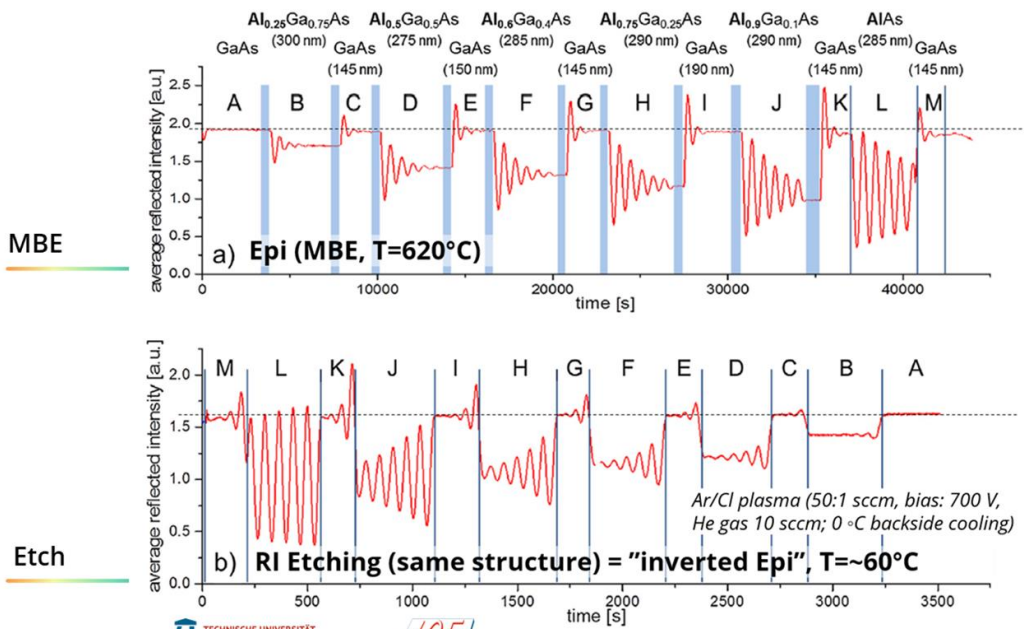
TEM

- ex-situ
- destructive



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- Integrated optical metrology, indispensable for high-yield energy production.
- Reflectometry for refractive index, growth/etch rate, etc.
- Deflectometry for wafer bowing quantification.
- Pyrometry for in-situ temperature control.





Thank you!

Knowledge is key

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Figure 4: Results of rebound effect on the average US-household annual electricity use for lighting. Original data from [HIC-15] modified by G. Zissis

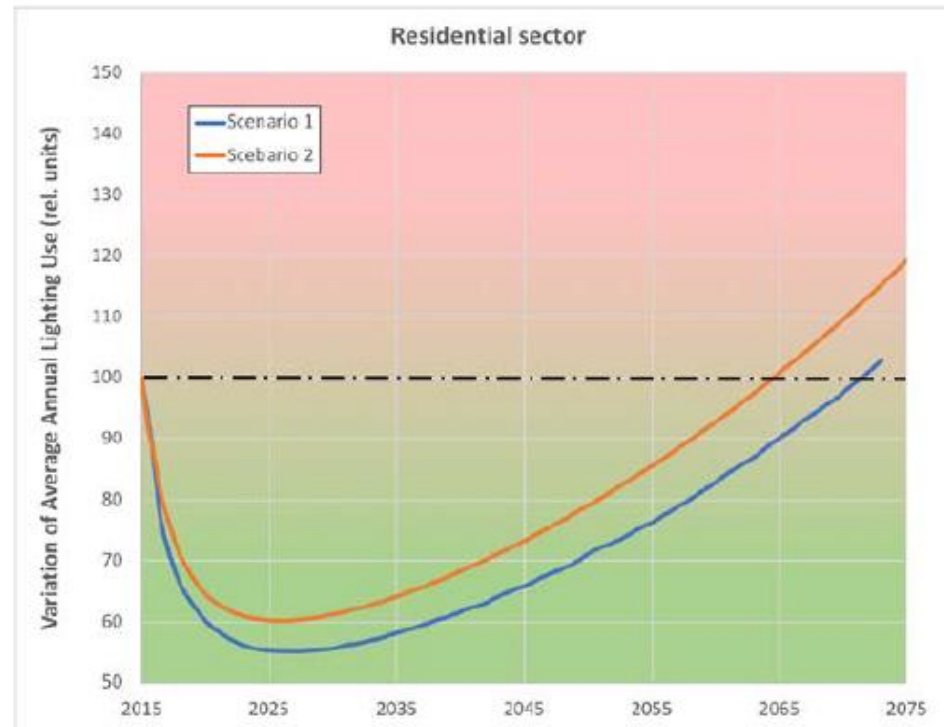


Figure 4 shows the impact of the rebound effect under 2 scenarios – Scenario 1: Individual households don't use more light as the cost of lighting decreases but population growth and increasing in housing size over time result in increase of energy demand for lighting; Scenario 2: Energy use increases over time because individual households demand more light as the cost of lighting decreases and lit areas increase as a result of population and housing area growths. Both scenarios show that the LED “effect” will vanish somewhere in between 2065 and 2070. This is not acceptable; solutions are then necessary to solve the issue. One potential solution consists on switching to smart human-centric lighting driven by both “application efficiency” and quality of light. **This just means that next gen lighting systems should provide the “Right Light” with the best efficiency and quality, when and where it is needed.**